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(54) METHOD AND SYSTEM FOR PROGRAMMING AND DRIVING ACTIVE MATRIX LIGHT EMITTING DEVICE PIXEL HAVING A CONTROLLABLE SUPPLY VOLTAGE

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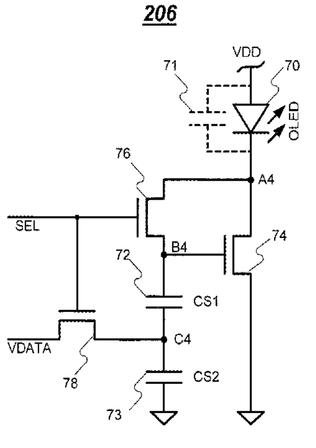
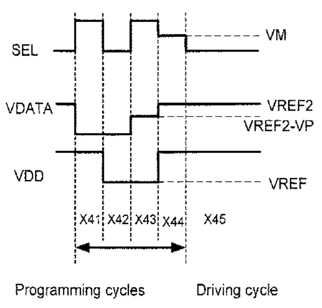
(57) ABSTRACT

Method and system for programming and driving active matrix light emitting device pixel is provided. The pixel is a voltage programmed pixel circuit, and has a light emitting device, a driving transistor and a storage capacitor. The pixel has a programming cycle having a plurality of operating cycles, and a driving cycle. During the programming cycle, the voltage of the connection between the OLED and the driving transistor is controlled so that the desired gate-source voltage of a driving transistor is stored in a storage capacitor.

15 Claims, 22 Drawing Sheets





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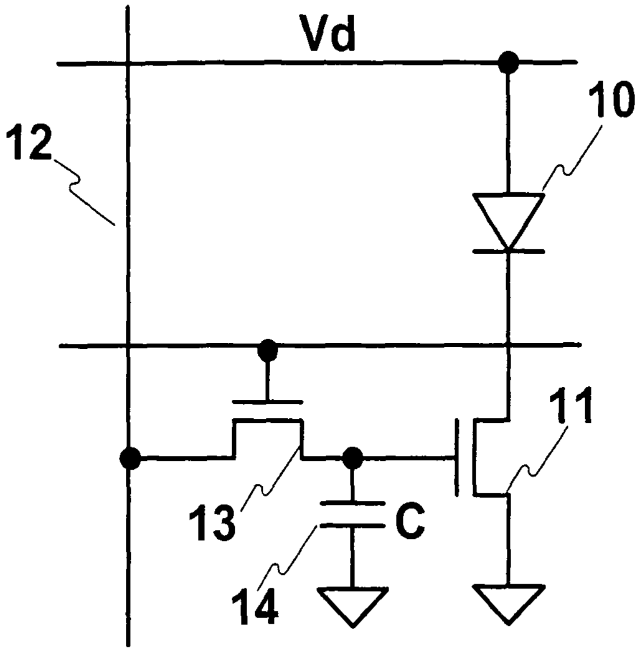


Figure 1

Prior Art

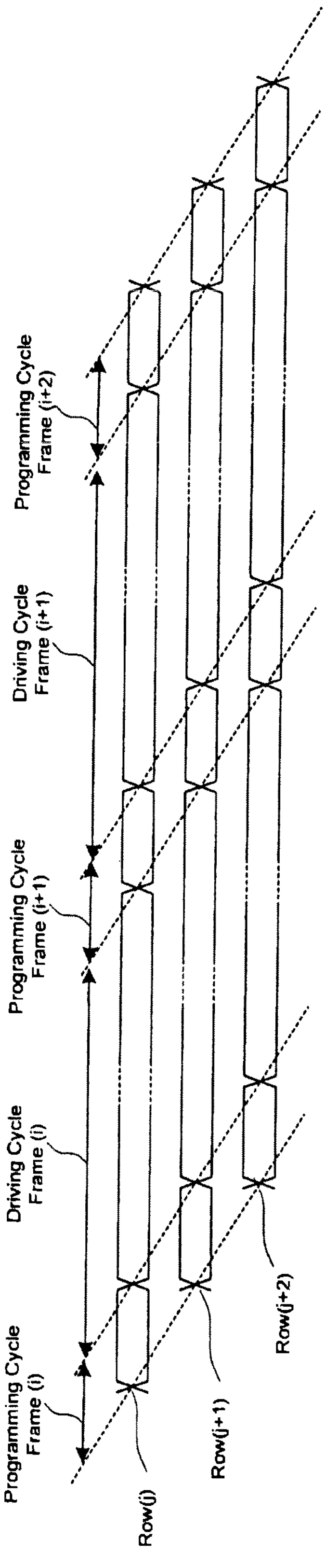
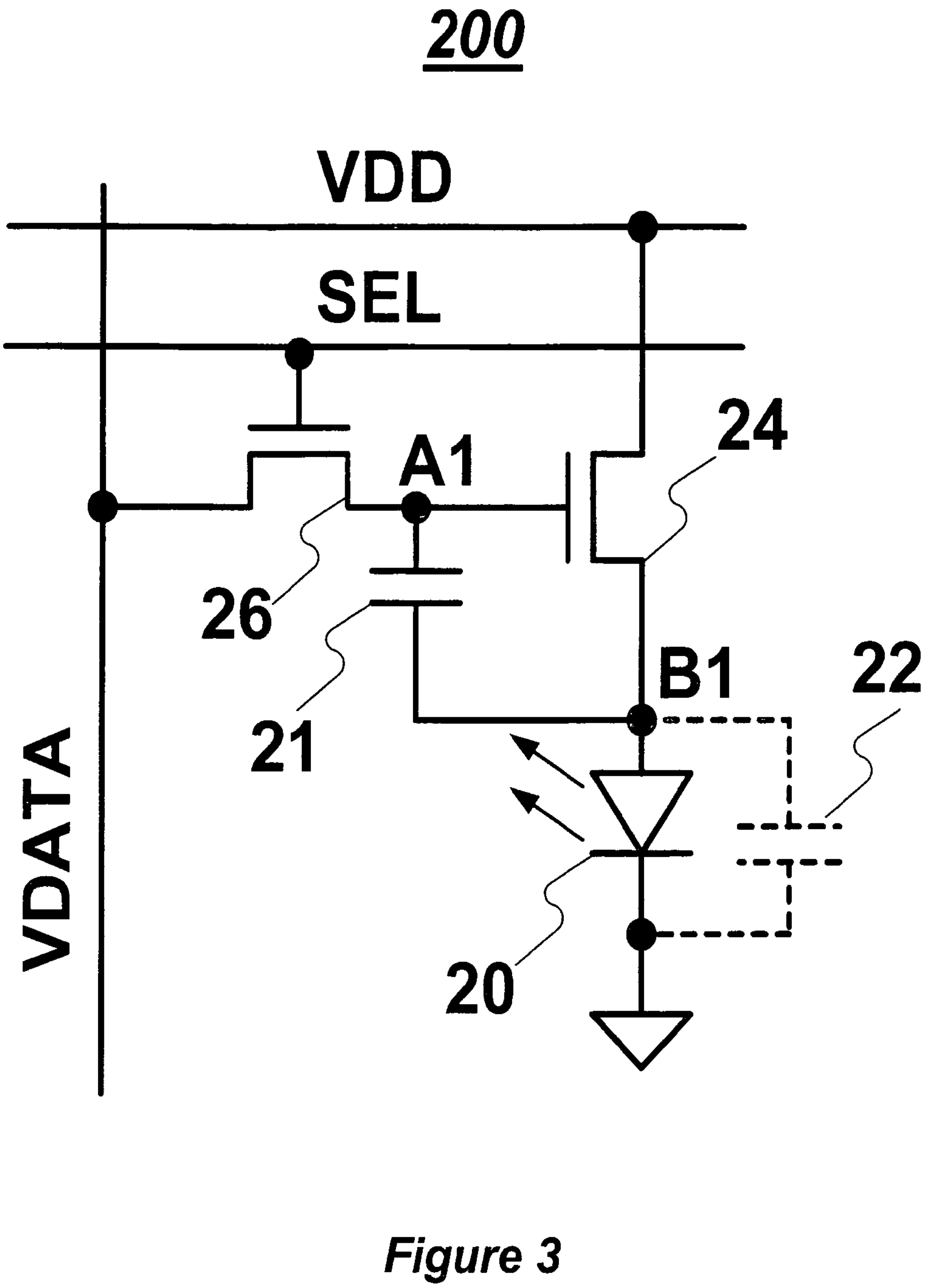

Programming Cycle
Frame (i)
Driving Cycle
Frame (i)
Programming Cycle
Frame (i+1)
Driving Cycle
Frame (i+1)
Programming Cycle
Frame (i+2)
Row(j)
Row(j+1)
Row(j+2)

Figure 2



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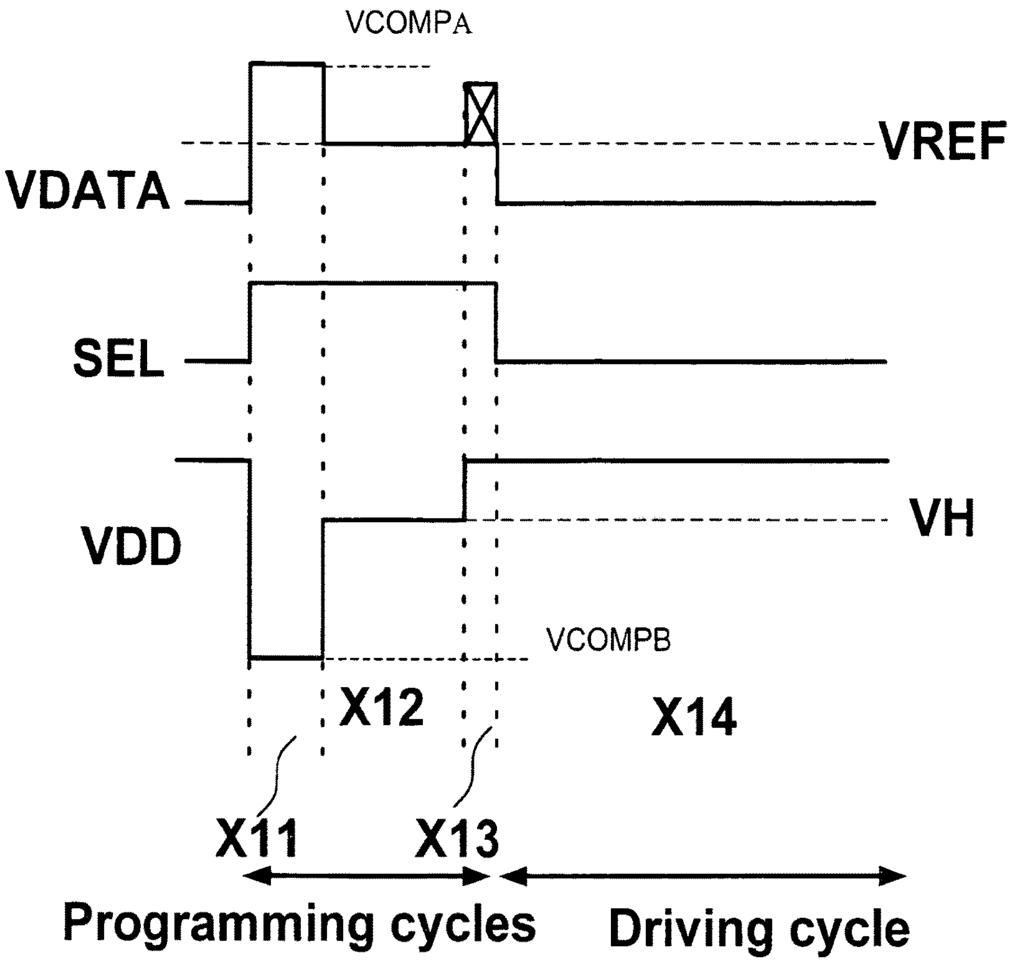
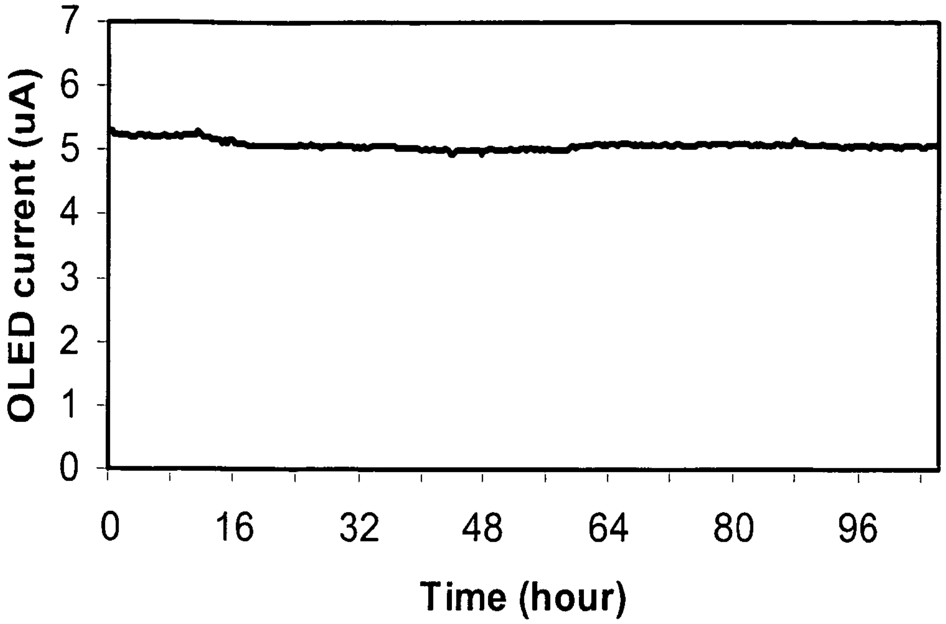

VCOMPA
VREF
VDATA
SEL
VDD
VH
VCOMPB
X12
X14
X11
X13
Programming cycles
Driving cycle

Figure 4



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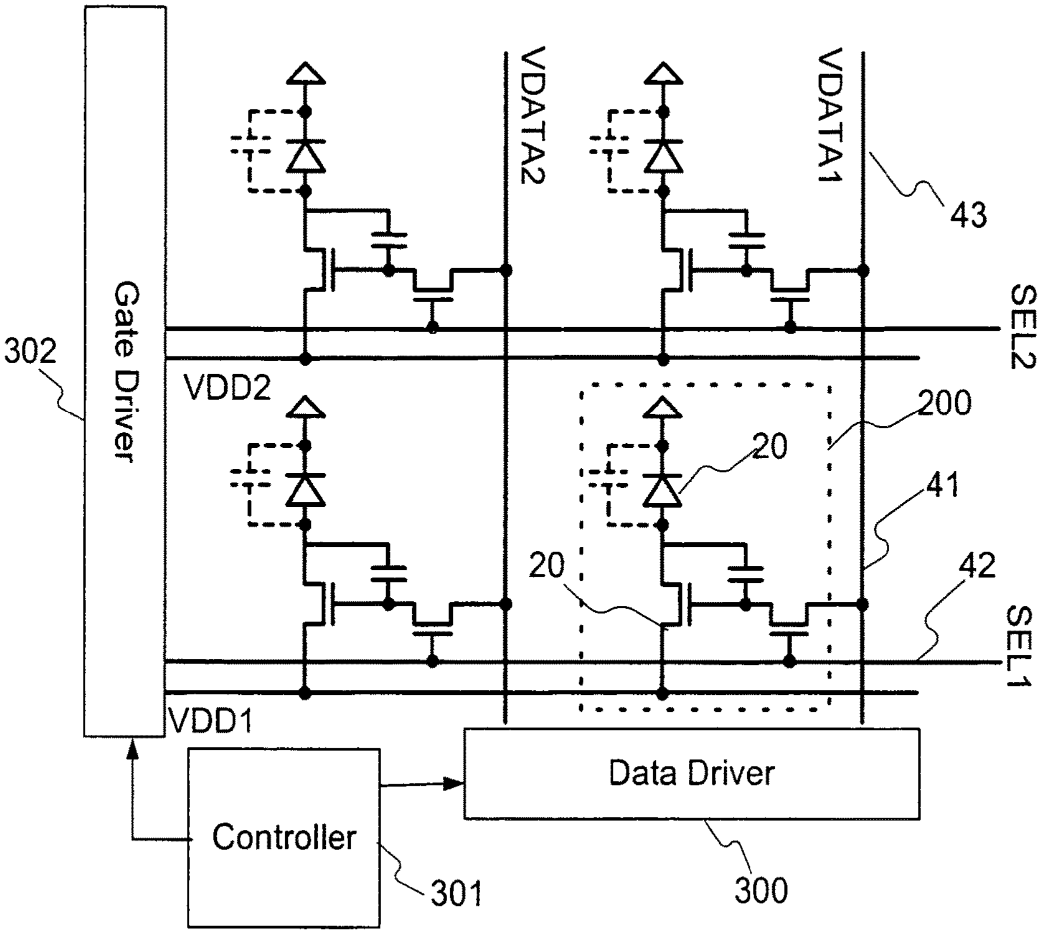
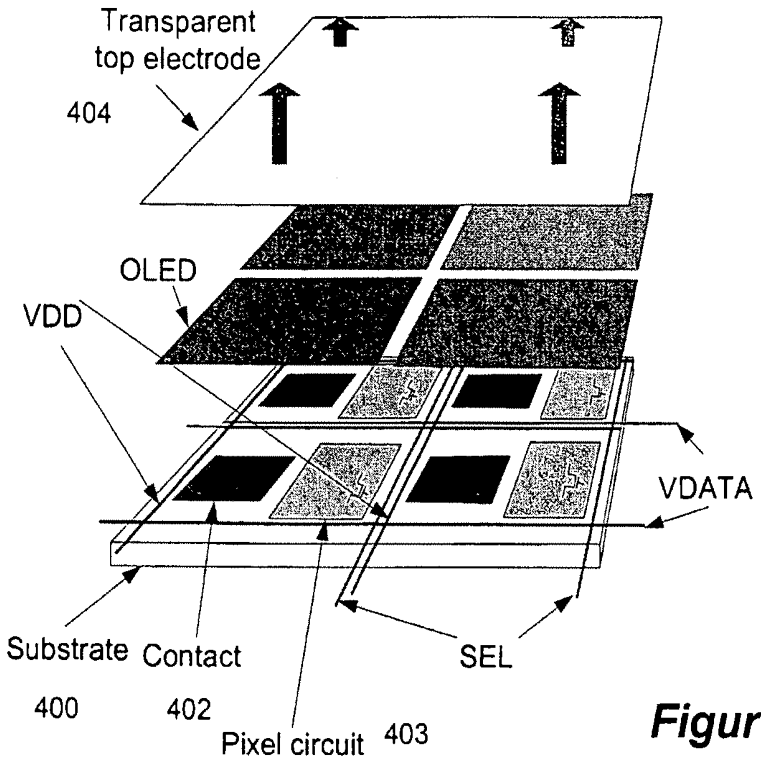
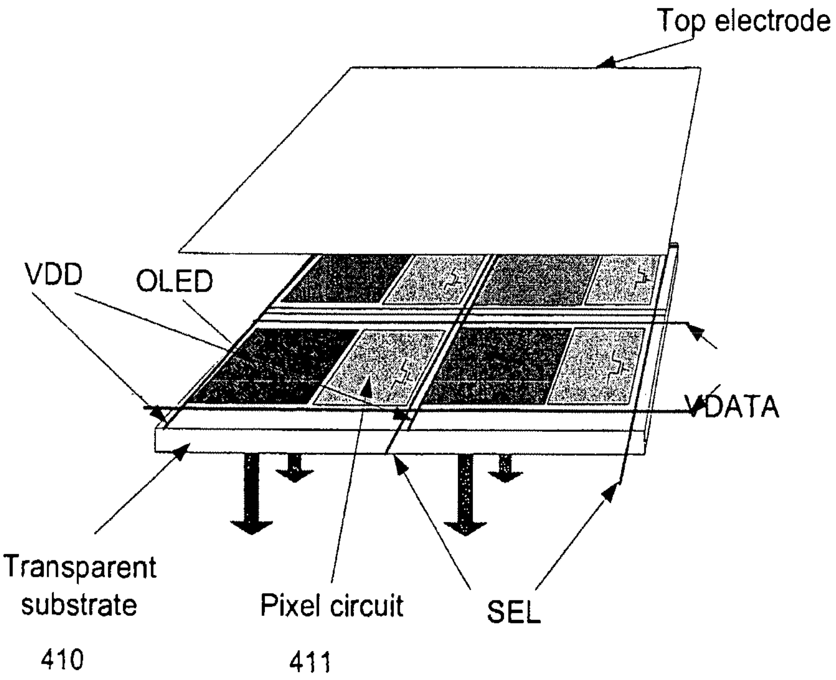

Gate Driver
302
VDATA2
VDATA1
43
SEL2
VDD2
200
20
41
20
42
SEL1
VDD1
Data Driver
Controller
301
300

Figure 6



Top emission pixels

Figure 7(a)



Bottom emission pixels

Figure 7(b)

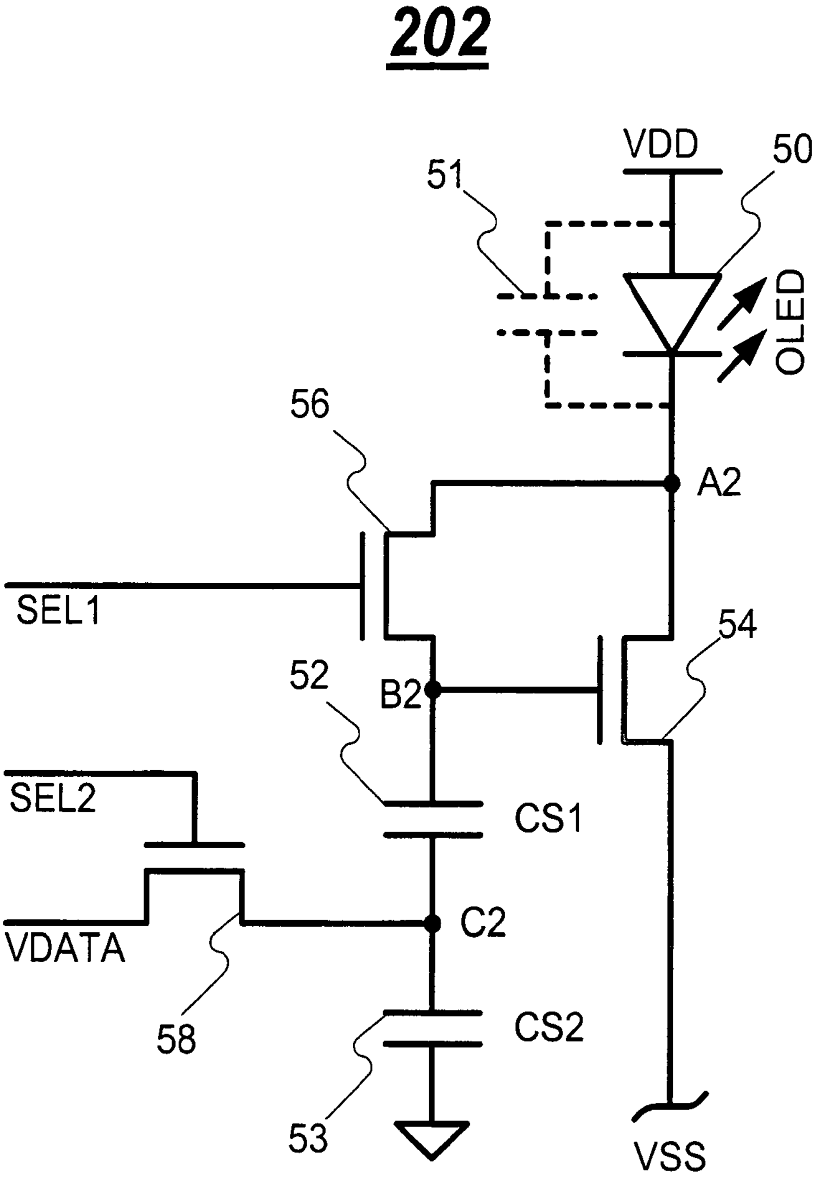

202
VDD
51
50
OLED
56
A2
SEL1
54
52
B2
SEL2
CS1
VDATA
C2
58
CS2
53
VSS

Figure 8

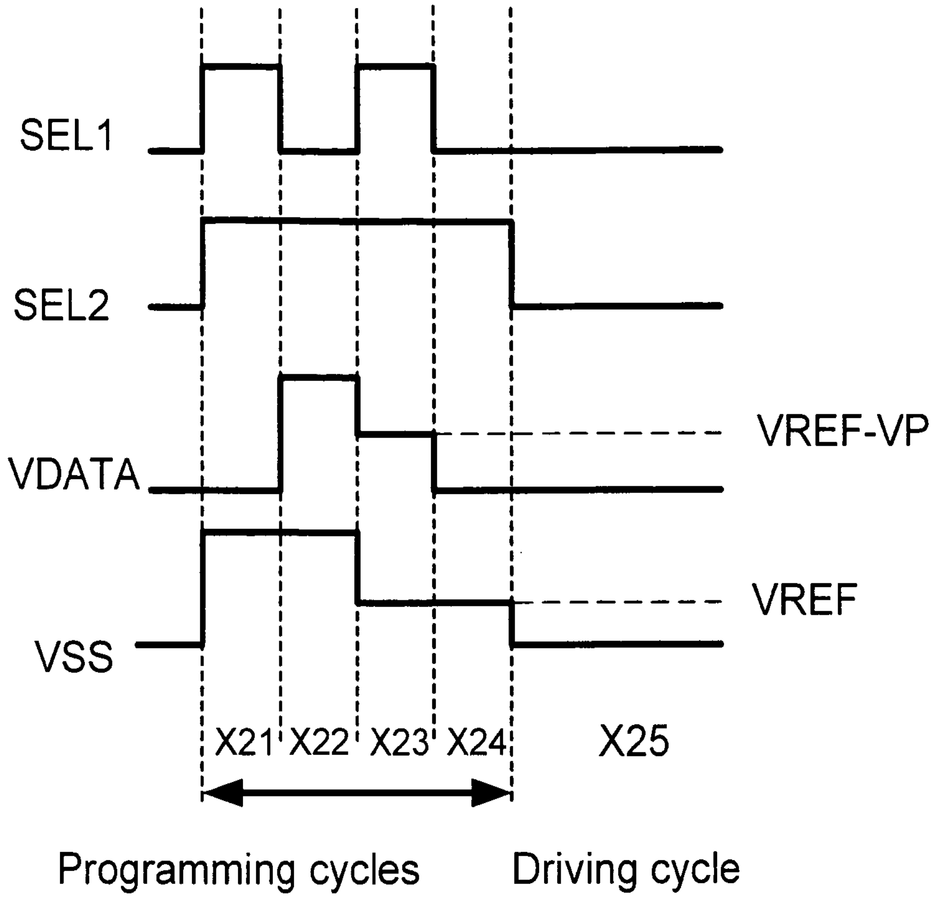
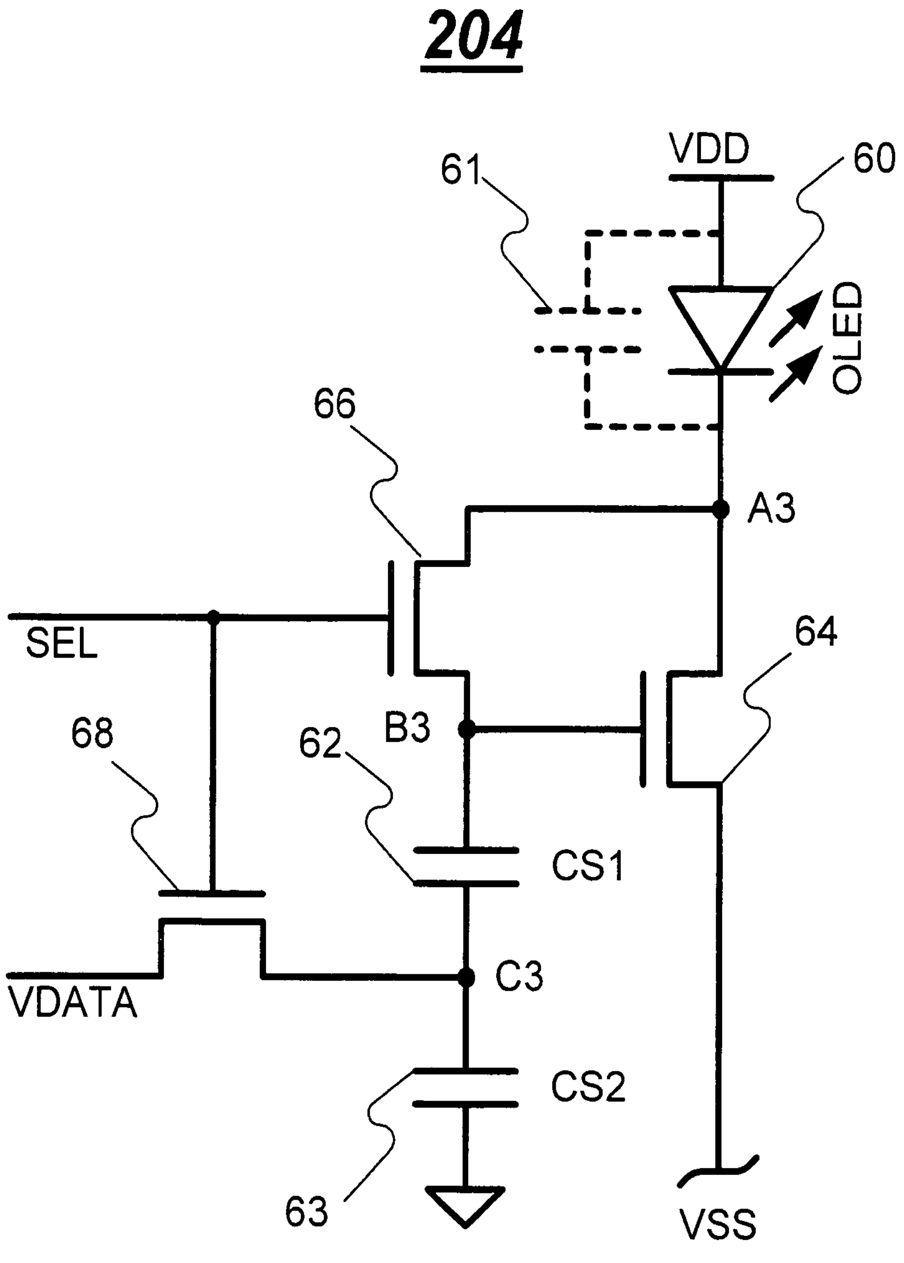

SEL1
SEL2
VDATA
VREF-VP
VSS
VREF
X21
X22
X23
X24
X25
Programming cycles
Driving cycle

Figure 9



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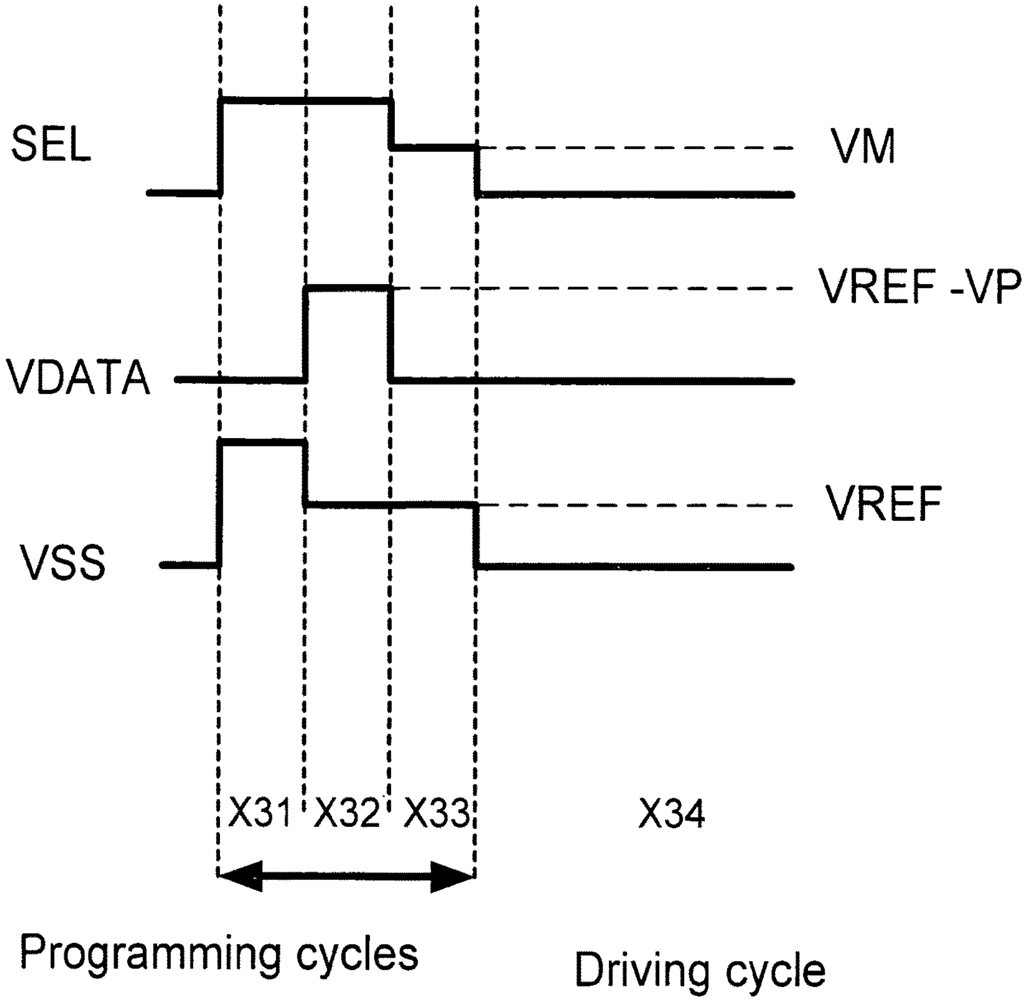
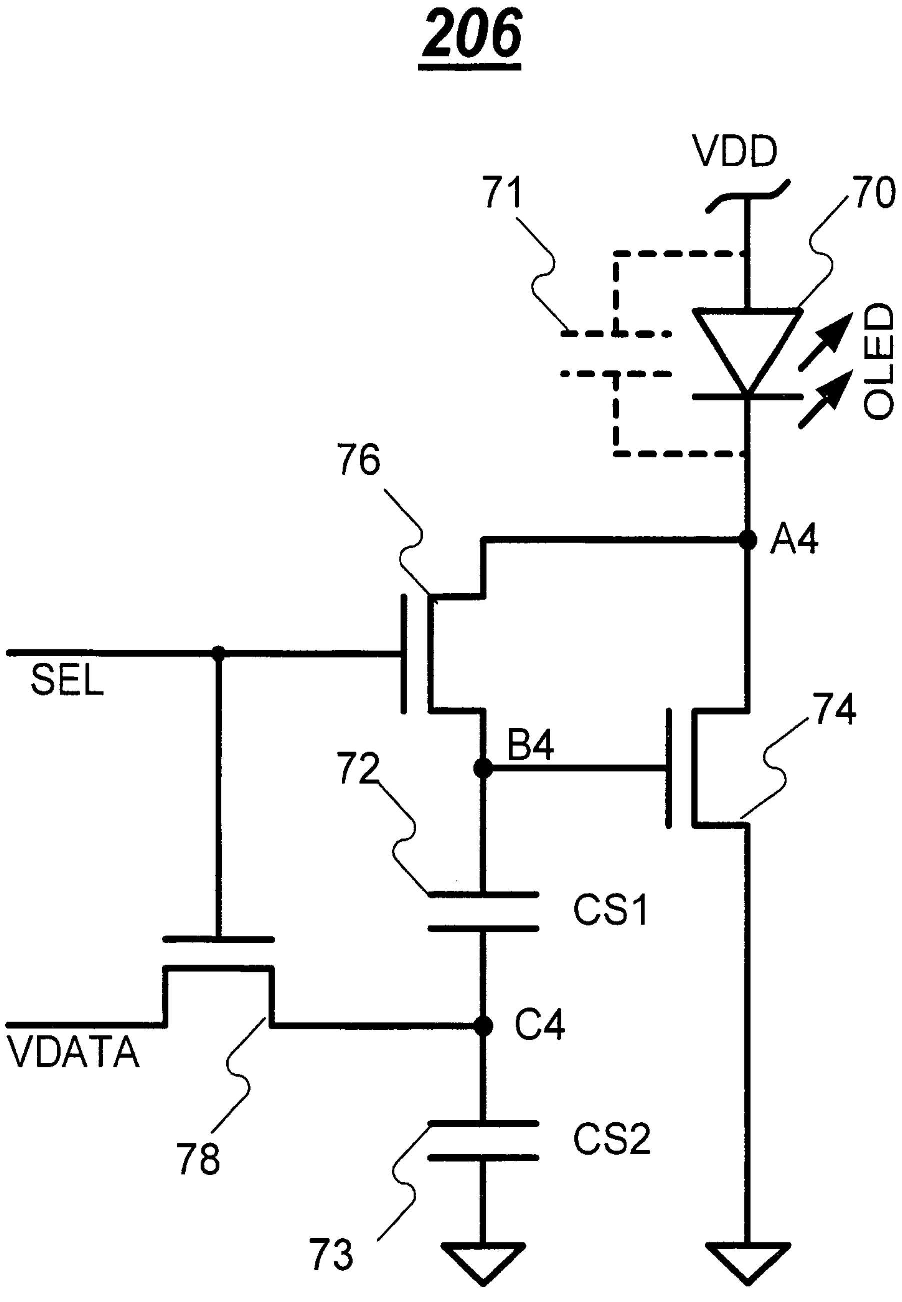

SEL
VM
VREF -VP
VDATA
VREF
VSS
X31
X32
X33
X34
Programming cycles
Driving cycle

Figure 11



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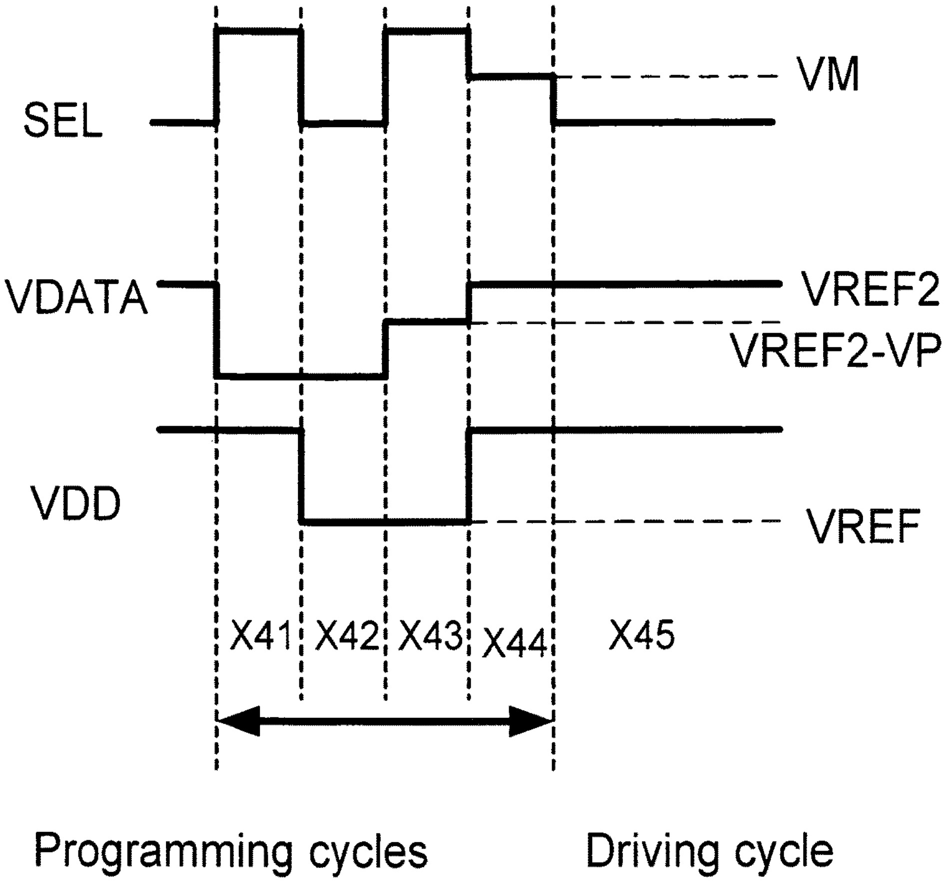
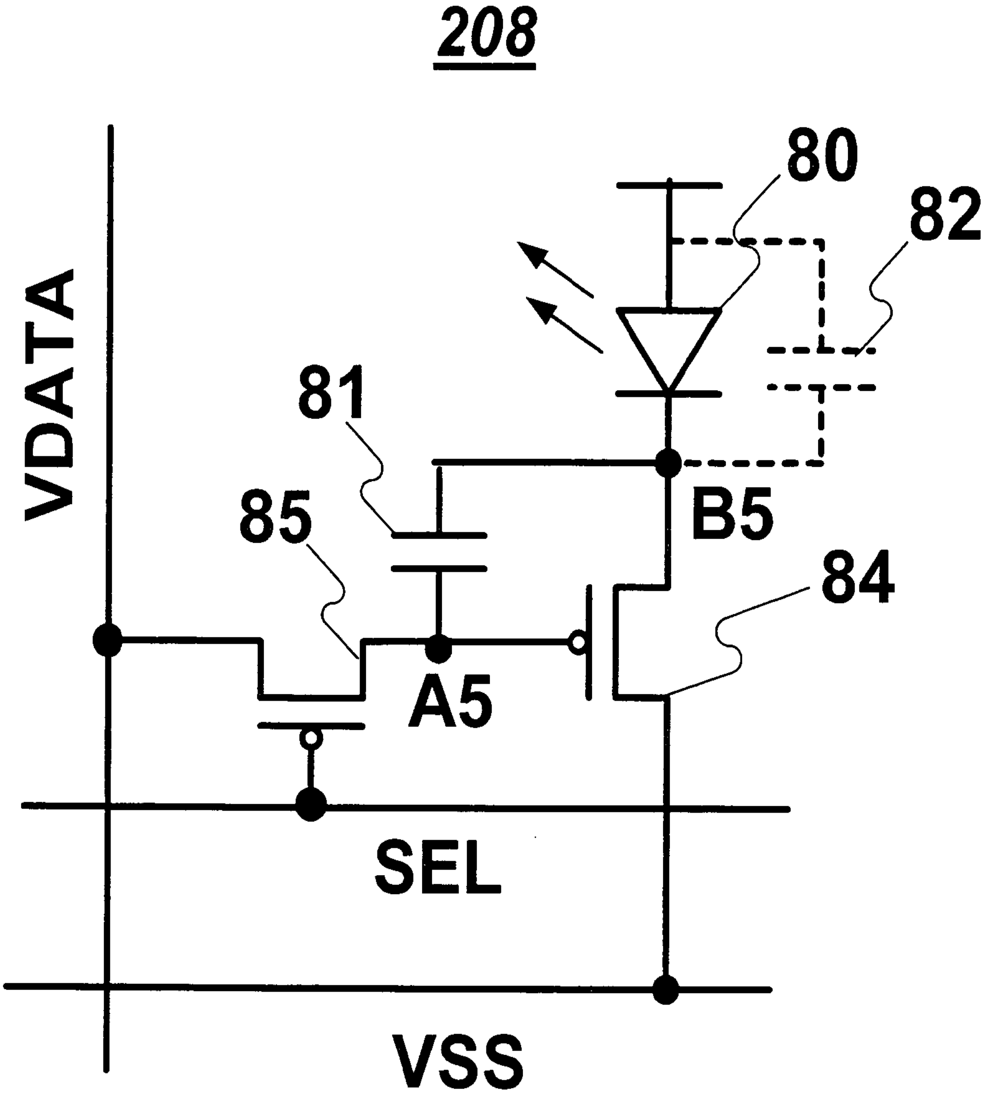

SEL
VM
VDATA
VREF2
VREF2-VP
VDD
VREF
X41
X42
X43
X44
X45
Programming cycles
Driving cycle

Figure 13



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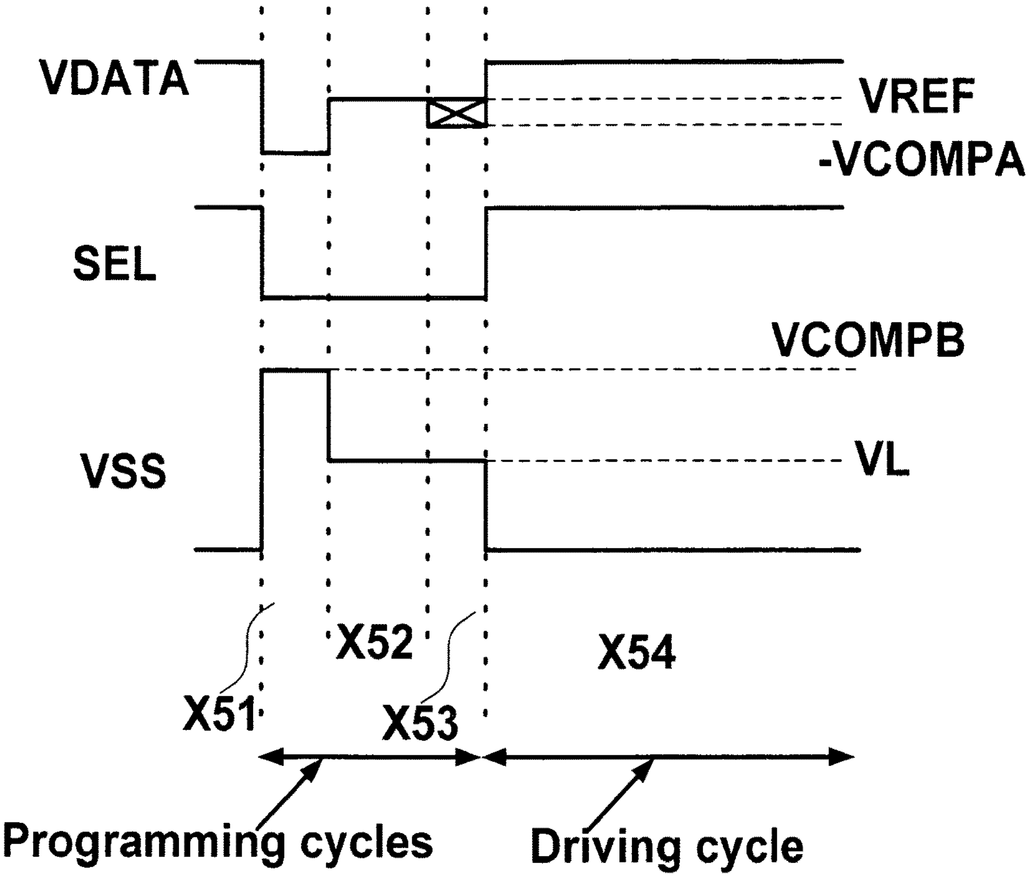

VDATA
VREF
-VCOMPA
SEL
VCOMPB
VSS
VL
X51
X52
X53
X54
Programming cycles
Driving cycle

Figure 15

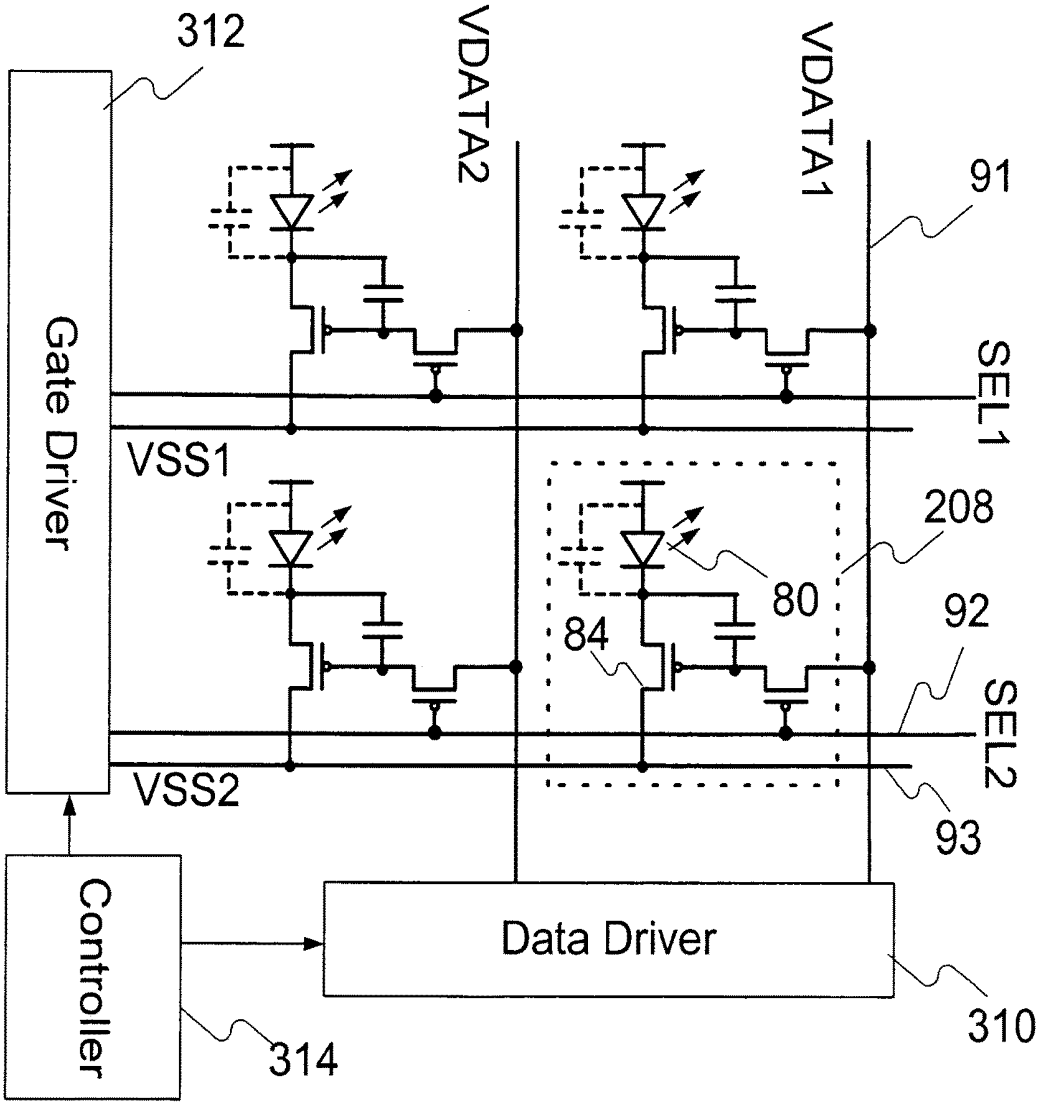

312
VDATA2
VDATA1
91
Gate Driver
SEL1
VSS1
208
80
84
92
SEL2
VSS2
93
Controller
Data Driver
314
310

Figure 16

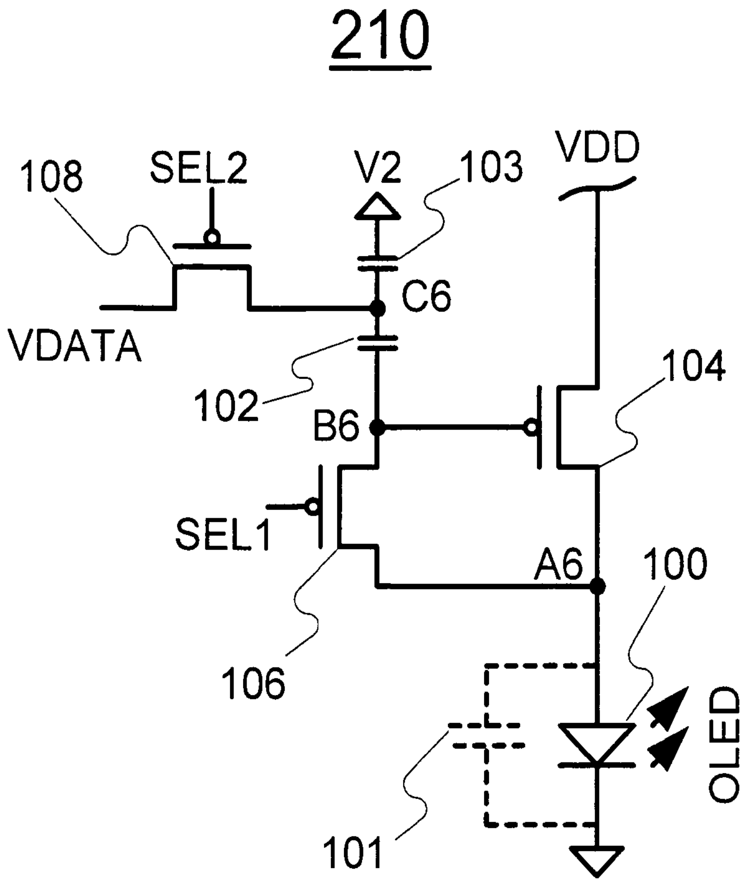

210
108
SEL2
V2
103
VDD
VDATA
C6
102
B6
104
SEL1
A6
100
106
101
OLED

Figure 17

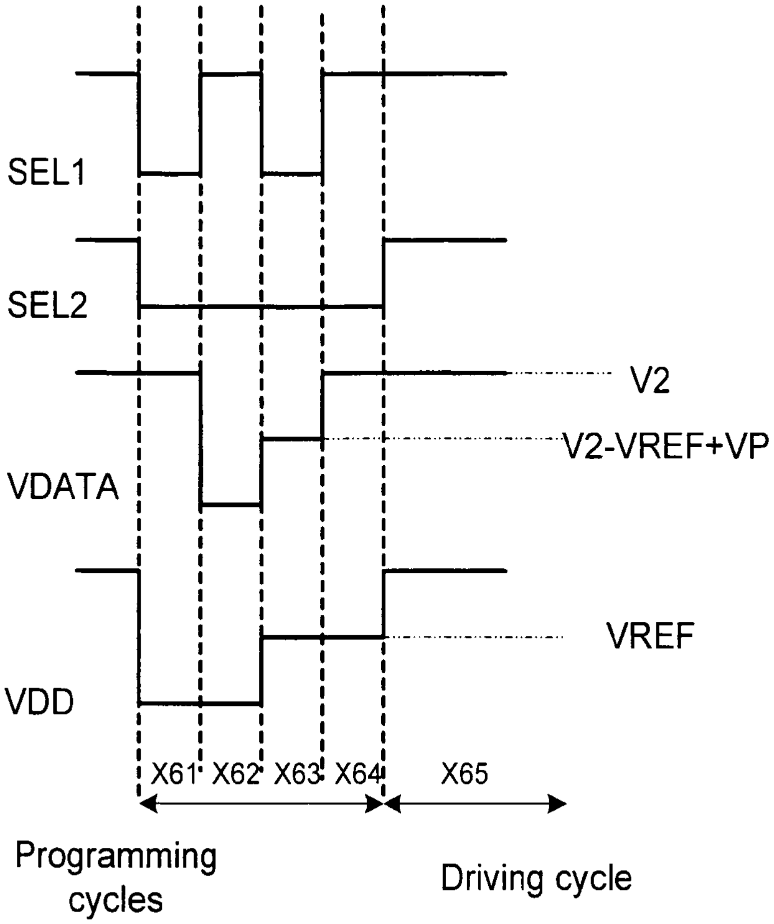
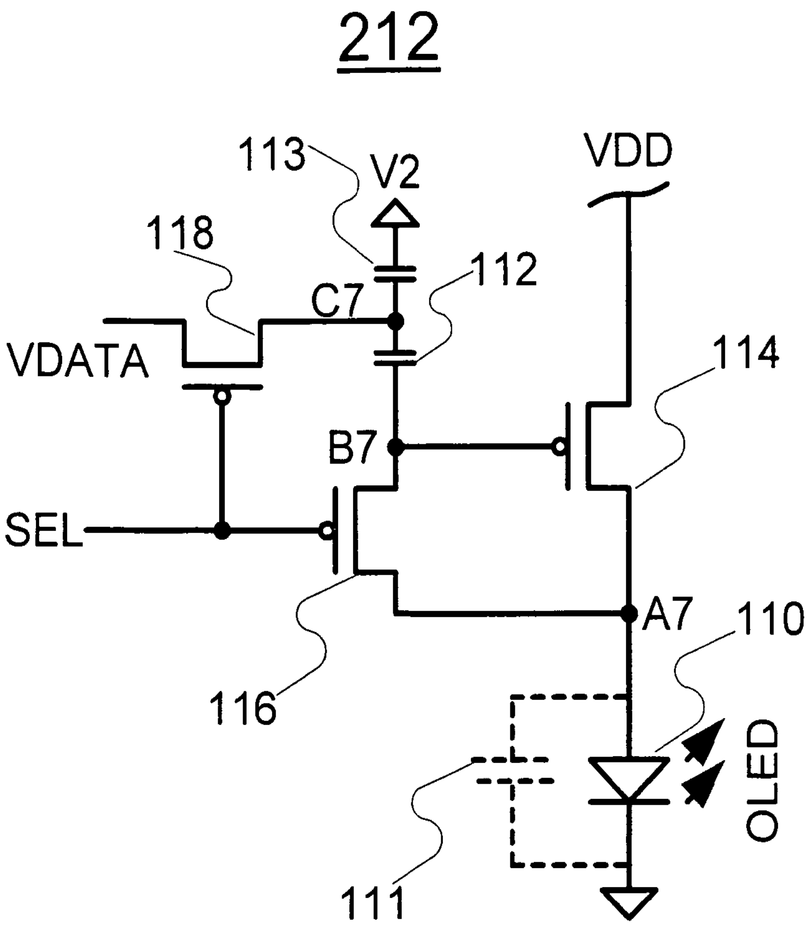

SEL1
SEL2
VDATA
VDD
V2
V2-VREF+VP
VREF
X61
X62
X63
X64
X65
Programming cycles
Driving cycle

Figure 18



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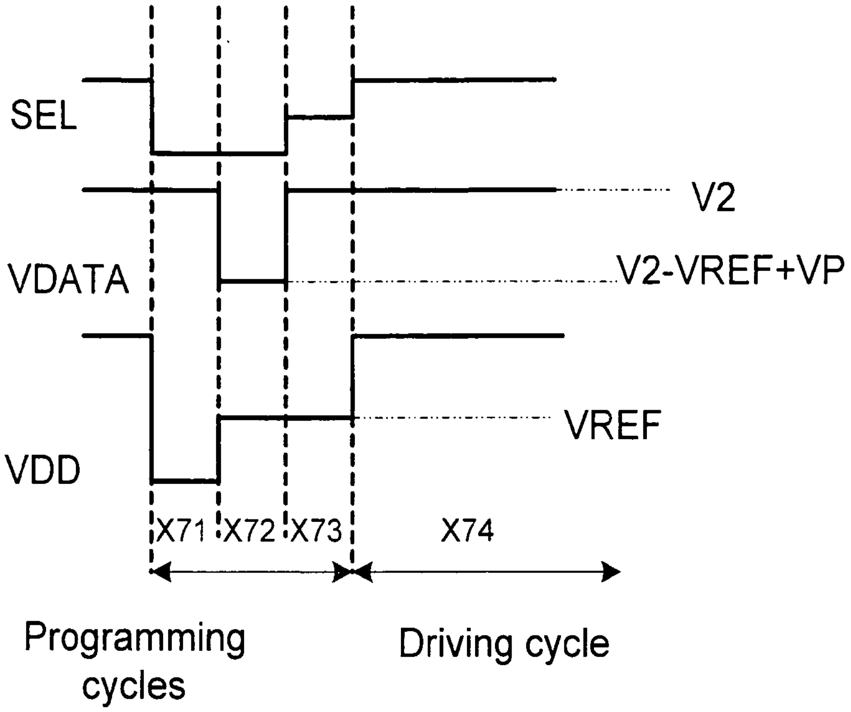
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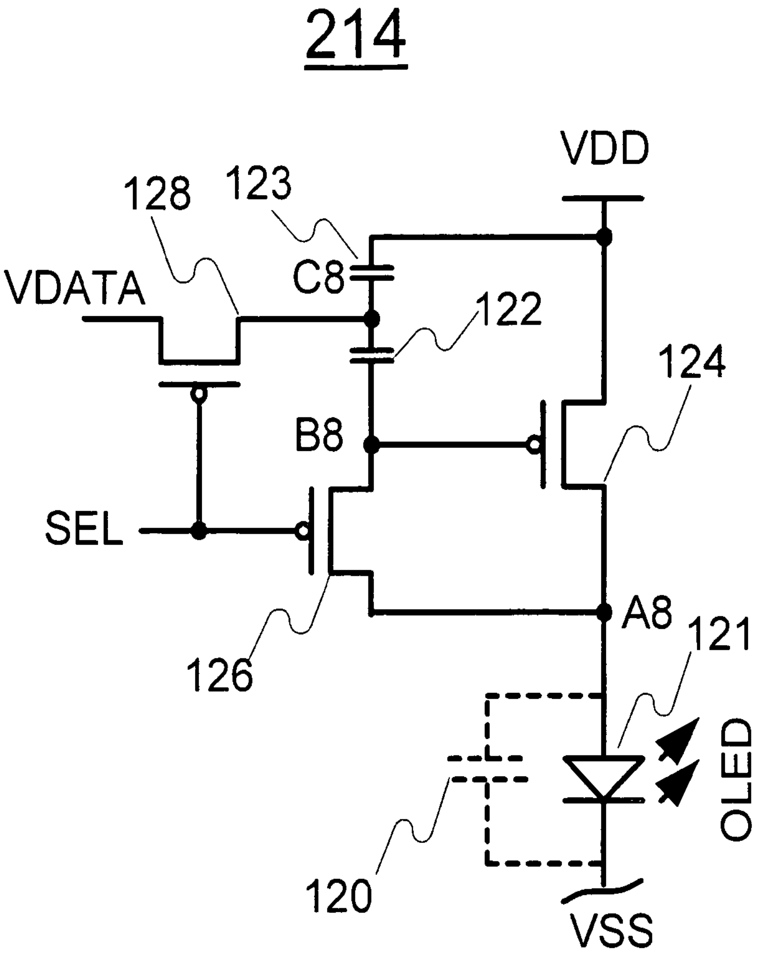
V2
VDATA
V2-VREF+VP
VREF
VDD
X71
X72
X73
X74
Programming cycles
Driving cycle

Figure 20



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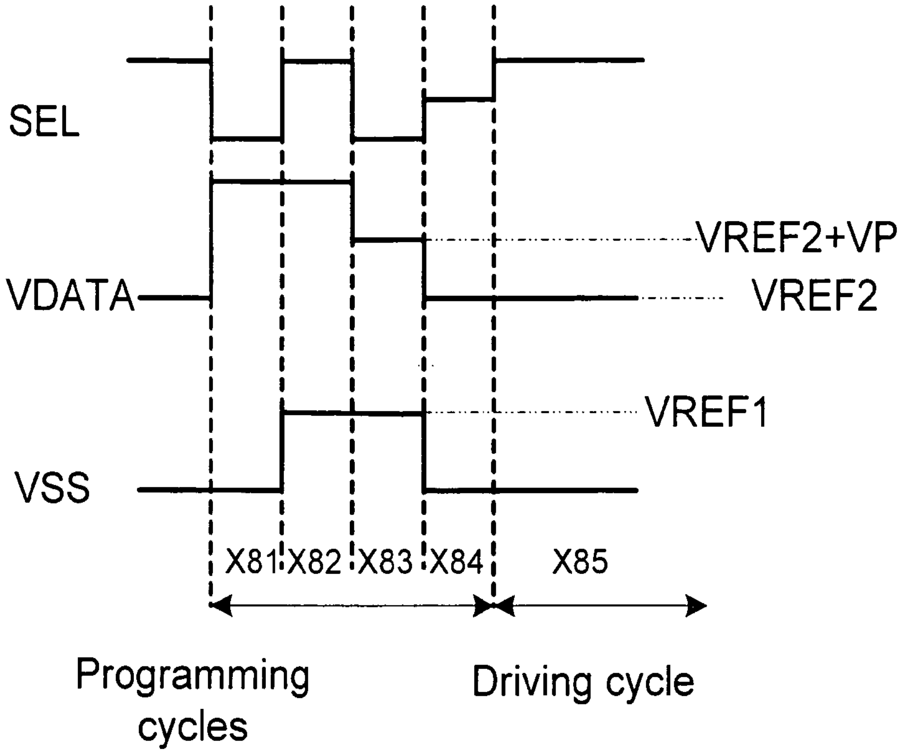
SEL
VDATA
VSS
VREF2+VP
VREF2
VREF1
X81
X82
X83
X84
X85
Programming cycles
Driving cycle

Figure 22

METHOD AND SYSTEM FOR PROGRAMMING AND DRIVING ACTIVE MATRIX LIGHT EMITTING DEVICE PIXEL HAVING A CONTROLLABLE SUPPLY VOLTAGE

CROSS REFERENCE TO RELATED APPLICATIONS

This application is a continuation of U.S. patent application Ser. No. 13/744,843, filed Jan. 18, 2013, now allowed, which is a continuation of U.S. patent application Ser. No. 13/243,065, filed Sep. 23, 2011, now issued as U.S. Pat. No. 8,378,938, which is a continuation of U.S. patent application Ser, No. 12/851,652, filed Aug. 6, 2010; now issued as U.S. Pat. No. 8,405,587, which is a continuation of U.S. patent application Ser. No. 11/298,240, filed Dec. 7, 2005, now issued as U.S. Pat. No. 7,800,565, which claims priority to Canadian Patent No. 2,490,858, filed Dec. 7, 2004, each of which is incorporated herein by reference in its entirety.

FIELD OF INVENTION

The present invention relates to a light emitting device displays, and more specifically to a driving technique for the light emitting device displays.

BACKGROUND OF THE INVENTION

Recently active-matrix organic light-emitting diode (AMOLED) displays with amorphous silicon (a-Si), poly-silicon, organic, or other driving backplane have become more attractive due to advantages over active matrix liquid crystal displays. An AMOLED display using a-Si backplanes, for example, has the advantages which include low temperature fabrication that broadens the use of different substrates and makes flexible displays feasible, and its low cost fabrication that yields high resolution displays with a wide viewing angle.

The AMOLED display includes an array of rows and columns of pixels, each having an organic light-emitting diode (OLED) and backplane electronics arranged in the array of rows and columns. Since the OLED is a current driven device, the pixel circuit of the AMOLED should be capable of providing an accurate and constant drive current.

FIG. **1** shows a pixel circuit as disclosed in U.S. Pat. No. 5,748,160. The pixel circuit of FIG. **1** includes an OLED **10**, a driving thin film transistor (TFT) **11**, a switch TFT **13**, and a storage capacitor **14**. The drain terminal of the driving TFT **11** is connected to the OLED **10**. The gate terminal of the driving TFT **11** is connected to a column line **12** through the switch TFT **13**. The storage capacitor **14**, which is connected between the gate terminal of the driving TFT **11** and the ground, is used to maintain the voltage at the gate terminal of the driving TFT **11** when the pixel circuit is disconnected from the column line **12**. The current through the OLED **10** strongly depends on the characteristic parameters of the driving TFT **11**. Since the characteristic parameters of the driving TFT **11**, in particular the threshold voltage under bias stress, vary by time, and such changes may differ from pixel to pixel, the induced image distortion may be unacceptably high.

U.S. Pat. No. 6,229,508 discloses a voltage-programmed pixel circuit which provides, to an OLED, a current independent of the threshold voltage of a driving TFT. In this pixel, the gate-source voltage of the driving TFT is composed of a programming voltage and the threshold voltage of the driving TFT. A drawback of U.S. Pat. No. 6,229,508 is that the pixel circuit requires extra transistors, and is complex, which results in a reduced yield, reduced pixel aperture, and reduced lifetime for the display.

Another method to make a pixel circuit less sensitive to a shift in the threshold voltage of the driving transistor is to use current programmed pixel circuits, such as pixel circuits disclosed in U.S. Pat. No. 6,734,636. In the conventional current programmed pixel circuits, the gate-source voltage of the driving TFT is self-adjusted based on the current that flows through it in the next frame, so that the OLED current is less dependent on the current-voltage characteristics of the driving TFT. A drawback of the current-programmed pixel circuit is that an overhead associated with low programming current levels arises from the column line charging time due to the large line capacitance.

SUMMARY OF THE INVENTION

It is an object of the invention to provide a method and system that obviates or mitigates at least one of the disadvantages of existing systems.

In accordance with an aspect to the present invention there is provided a method of programming and driving a display system, the display system includes: a display array having a plurality of pixel circuits arranged in row and column, each pixel circuit having: a light emitting device having a first terminal and a second terminal, the first terminal of the lighting device being connected to a voltage supply electrode; a capacitor having a first terminal and a second terminal; a switch transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the switch transistor being connected to a select line, the first terminal of the switch transistor being connected to a signal line for transferring voltage data, the second terminal of the switch transistor being connected to the first terminal of the capacitor; and a driving transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the driving transistor being connected to the second terminal of the switch transistor and the first terminal of the capacitor at a first node (A), the first terminal of the driving transistor being connected to the second terminal of the light emitting device and the second terminal of the capacitor at a second node (B), the second terminal of the driving transistor being connected to a controllable voltage supply line; a driver for driving the select line, the controllable voltage supply line and the signal line to operate the display array; the method including the steps of: at a programming cycle, at a first operating cycle, charging the second node at a first voltage defined by (VREF−VT) or (−VREF+VT), where VREF represents a reference voltage and VT represents a threshold voltage of the driving transistor; at a second operating cycle, charging the first node at a second voltage defined by (VREF+VP) or (−VREF+VP) so that the difference between the first and second node voltages is stored in the storage capacitor, where VP represents a programming voltage; at a driving cycle, applying the voltage stored in the storage capacitor to the gate terminal of the driving transistor.

In accordance with a further aspect to the present invention there is provided a method of programming and driving a display system, the display system includes: a display array having a plurality of pixel circuits arranged in row and column, each pixel circuit having: a light emitting device having a first terminal and a second terminal, the first terminal of the lighting device being connected to a voltage supply electrode; a first capacitor and a second capacitor, each having a first terminal and a second terminal; a first switch transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the first switch transistor being connected to a first select line, the first terminal of the first switch transistor being connected to the second terminal of the light emitting device, the second terminal of the first switch being connected to the first terminal of the first capacitor; a second switch transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the second switch transistor being connected to a second select line, the first terminal of the second switch transistor being connected to a signal line for transferring voltage data; a driving transistor having a gate terminal, a first terminal and a second terminal, the first terminal of the driving transistor being connected to the second terminal of the light emitting device at a first node (A), the gate terminal of the driving transistor being connected to the second terminal of the first switch transistor and the first terminal of the first capacitor at a second node (B), the second terminal of the driving transistor being connected to a controllable voltage supply line; the second terminal of the second switch transistor being connected to the second terminal of the first capacitor and the first terminal of the second capacitor at a third node (C); a driver for driving the first and second select line, the controllable voltage supply line and the signal line to operate the display array, the method including the steps of: at a programming cycle, at a first operating cycle, controlling the voltage of each of the first node and the second node so as to store (VT+VP) or −(VT+VP) in the first storage capacitor, where VT represents a threshold voltage of the driving transistor, VP represents a programming voltage; at a second operating cycle, discharging the third node; at a driving cycle, applying the voltage stored in the storage capacitor to the gate terminal of the driving transistor.

In accordance with a further aspect to the present invention there is provided a display system including: a display array having a plurality of pixel circuits arranged in row and column, each pixel circuit having: a light emitting device having a first terminal and a second terminal, the first terminal of the lighting device being connected to a voltage supply electrode; a capacitor having a first terminal and a second terminal; a switch transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the switch transistor being connected to a select line, the first terminal of the switch transistor being connected to a signal line for transferring voltage data, the second terminal of the switch transistor being connected to the first terminal of the capacitor; and a driving transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the driving transistor being connected to the second terminal of the switch transistor and the first terminal of the capacitor at a first node (A), the first terminal of the driving transistor being connected to the second terminal of the light emitting device and the second terminal of the capacitor at a second node (B), the second terminal of the driving transistor being connected to a controllable voltage supply line; a driver for driving the select line, the controllable voltage supply line and the signal line to operate the display array; and a controller for implementing a programming cycle and a driving cycle on each row of the display array using the driver; wherein the programming cycle includes a first operating cycle and a second operating cycle, wherein at the first operating cycle, the second node is charged at a first voltage defined by (VREF−VT) or (−VREF+VT), where VREF represents a reference voltage and VT represents a threshold voltage of the driving transistor, at the second operating cycle, the first node is charged at a second voltage defined by (VREF+VP) or (−VREF+VP) so that the difference between the first and second node voltages is stored in the storage capacitor, where VP represents a programming voltage; wherein at the driving cycle, the voltage stored in the storage capacitor is applied to the gate terminal of the driving transistor.

In accordance with a further aspect to the present invention there is provided a display system including: a display array having a plurality of pixel circuits arranged in row and column, each pixel circuit having: a light emitting device having a first terminal and a second terminal, the first terminal of the lighting device being connected to a voltage supply electrode; a first capacitor and a second capacitor, each having a first terminal and a second terminal; a first switch transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the first switch transistor being connected to a first select line, the first terminal of the first switch transistor being connected to the second terminal of the light emitting device, the second terminal of the first switch being connected to the first terminal of the first capacitor; a second switch transistor having a gate terminal, a first terminal and a second terminal, the gate terminal of the second switch transistor being connected to a second select line, the first terminal of the second switch transistor being connected to a signal line for transferring voltage data; a driving transistor having a gate terminal, a first terminal and a second terminal, the first terminal of the driving transistor being connected to the second terminal of the light emitting device at a first node (A), the gate terminal of the driving transistor being connected to the second terminal of the first switch transistor and the first terminal of the first capacitor at a second node (B), the second terminal of the driving transistor being connected to a controllable voltage supply line; the second terminal of the second switch transistor being connected to the second terminal of the first capacitor and the first terminal of the second capacitor at a third node (C); a driver for driving the first and second select line, the controllable voltage supply line and the signal line to operate the display array; and a controller for implementing a programming cycle and a driving cycle on each row of the display array using the driver; wherein the programming cycle includes a first operating cycle and a second operating cycle, wherein at the first operating cycle, the voltage of each of the first node and the second node is controlled so as to store (VT+VP) or −(VT+VP) in the first storage capacitor, where VT represents a threshold voltage of the driving transistor, VP represents a programming voltage, at the second operating cycle, the third node is discharged, wherein at the driving cycle, the voltage stored in the storage capacitor is applied to the gate terminal of the driving transistor.

This summary of the invention does not necessarily describe all features of the invention.

Other aspects and features of the present invention will be readily apparent to those skilled in the art from a review of the following detailed description of preferred embodiments in conjunction with the accompanying drawings.

BRIEF DESCRIPTION OF THE DRAWINGS

These and other features of the invention will become more apparent from the following description in which reference is made to the appended drawings wherein:

FIG. **1** is a diagram showing a conventional 2-TFT voltage programmed pixel circuit;

FIG. **2** is a timing diagram showing an example of programming and driving cycles in accordance with an embodiment of the present invention, which is applied to a display array;

FIG. **3** is a diagram showing a pixel circuit to which programming and driving technique in accordance with an embodiment of the present invention is applied;

FIG. **4** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **3**;

FIG. **5** is a diagram showing a lifetime test result for the pixel circuit of FIG. **3**;

FIG. **6** is a diagram showing a display system having the pixel circuit of FIG. **3**;

FIG. **7**(*a*) is a diagram showing an example of the array structure having top emission pixels which are applicable to the array of FIG. **6**;

FIG. **7**(*b*) is a diagram showing an example of the array structure having bottom emission pixels which are applicable to the array of FIG. **6**;

FIG. **8** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied;

FIG. **9** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **8**;

FIG. **10** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied;

FIG. **11** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **10**;

FIG. **12** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied;

FIG. **13** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **12**;

FIG. **14** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied;

FIG. **15** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **14**;

FIG. **16** is a diagram showing a display system having the pixel circuit of FIG. **14**;

FIG. **17** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied;

FIG. **18** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **17**;

FIG. **19** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied;

FIG. **20** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **19**;

FIG. **21** is a diagram showing a pixel circuit to which programming and driving technique in accordance with a further embodiment of the present invention is applied; and

FIG. **22** is a timing diagram showing an example of waveforms for programming and driving the pixel circuit of FIG. **21**;

DETAILED DESCRIPTION OF THE PREFERRED EMBODIMENTS OF THE INVENTION

Embodiments of the present invention are described using a pixel having an organic light emitting diode (OLED) and a driving thin film transistor (TFT). However, the pixel may include any light emitting device other than OLED, and the pixel may include any driving transistor other than TFT. It is noted that in the description, "pixel circuit" and "pixel" may be used interchangeably.

FIG. **2** is a diagram showing programming and driving cycles in accordance with an embodiment of the present invention. In FIG. **2**, each of ROW(j), ROW(j+1), and ROW(j+2) represents a row of the display array where a plurality of pixel circuits are arranged in row and column.

The programming and driving cycle for a frame occurs after the programming and driving cycle for a next frame. The programming and driving cycles for the frame at a ROW overlaps with the programming and driving cycles for the same frame at a next ROW. As described below, during the programming cycle, the time depending parameter(s) of the pixel circuit is extracted to generate a stable pixel current.

FIG. **3** illustrates a pixel circuit **200** to which programming and driving technique in accordance with an embodiment of the present invention is applied. The pixel circuit **200** includes an OLED **20**, a storage capacitor **21**, a driving transistor **24**, and a switch transistor **26**. The pixel circuit **200** is a voltage programmed pixel circuit. Each of the transistors **24** and **26** has a gate terminal, a first terminal and a second terminal. In the description, the first terminal (second terminal) may be, but not limited to, a drain terminal or a source terminal (a source terminal or a drain terminal).

The transistors **24** and **26** are n-type TFTs. However, the transistors **24** and **26** may be p-type transistors. As described below, the driving technique applied to the pixel circuit **200** is also applicable to a complementary pixel circuit having p-type transistors as shown in FIG. **14**. The transistors **24** and **26** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), NMOS/PMOS technology or CMOS technology (e.g. MOSFET).

The first terminal of the driving transistor **24** is connected to a controllable voltage supply line VDD. The second terminal of the driving transistor **24** is connected to the anode electrode of the OLED **20**. The gate terminal of the driving transistor **24** is connected to a signal line VDATA through the switch transistor **26**. The storage capacitor **21** is connected between the source and gate terminals of the driving transistor **24**.

The gate terminal of the switch transistor **26** is connected to a select line SEL. The first terminal of the switch transistor **26** is connected to the signal line VDATA. The second terminal of the switch transistor **26** is connected to the gate terminal of the driving transistor **24**. The cathode electrode of the OLED **20** is connected to a ground voltage supply electrode.

The transistors **24** and **26** and the storage capacitor **21** are connected at node A**1**. The transistor **24**, the OLED **20** and the storage capacitor **21** are connected at node B**1**.

FIG. **4** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **200** of FIG. **3**. Referring to FIGS. **3** and **4**, the operation of the pixel circuit **200** includes a programming cycle having three operating cycles X**11**, X**12** and X**13**, and a driving cycle having one operating cycle X**14**.

During the programming cycle, node B**1** is charged to the negative threshold voltage of the driving transistor **24**, and node A**1** is charged to a programming voltage VP.

As a result, the gate-source voltage of the driving transistor **24** goes to:

$$VGS=VP-(-VT)=VP+VT \tag{1}$$

where VGS represents the gate-source voltage of the driving transistor **24**, and VT represents the threshold voltage of the driving transistor **24**.

Since the driving transistor **24** is in saturation regime of operation, its current is defined mainly by its gate-source voltage. As a result the current of the driving transistor **24** remains constant even if the OLED voltage changes, since its gate-source voltage is stored in the storage capacitor **21**.

In the first operating cycle X**11**: VDD goes to a compensating voltage VCOMPB, and VDATA goes to a high positive compensating voltage VCOMPA, and SEL is high. As a result, node A**1** is charged to VCOMPA and node B**1** is charged to VCOMPB.

In the second operating cycle X**12**: While VDATA goes to a reference voltage VREF, node B**1** is discharged through the driving transistor **24** until the driving transistor **24** turns off. As a result, the voltage of node B**1** reaches (VREF−VT). VDD has a positive voltage VH to increase the speed of this cycle X**12**. For optimal setting time, VH can be set to be equal to the operating voltage which is the voltage on VDD during the driving cycle.

In the third operating cycle X**13**: VDD goes to its operating voltage. While SEL is high, node A**1** is charged to (VP+VREF). Because the capacitance **22** of the OLED **20** is large, the voltage at node B**1** stays at the voltage generated in the previous cycle X**12**. Thus, the voltage of node B**1** is (VREF−VT). Therefore, the gate-source voltage of the driving transistor **24** is (VP+VT), and this gate-source voltage is stored in the storage capacitor **21**.

In the fourth operating cycle X**14**: SEL and VDATA go to zero. VDD is the same as that of the third operating cycle X**13**. However, VDD may be higher than that of the third operating cycle X**13**. The voltage stored in the storage capacitor **21** is applied to the gate terminal of the driving transistor **24**. Since the gate-source voltage of the driving transistor **24** include its threshold voltage and also is independent of the OLED voltage, the degradation of the OLED **20** and instability of the driving transistor **24** does not affect the amount of current flowing through the driving transistor **24** and the OLED **20**.

It is noted that the pixel circuit **200** can be operated with different values of VCOMPB, VCOMPA, VP, VREF and VH. VCOMPB, VCOMPA, VP, VREF and VH define the lifetime of the pixel circuit **200**. Thus, these voltages can be defined in accordance with the pixel specifications.

FIG. **5** illustrates a lifetime test result for the pixel circuit and waveform shown in FIGS. **3** and **4**. In the test, a fabricated pixel circuit was put under the operation for a long time while the current of the driving transistor (**24** of FIG. **3**) was monitored to investigate the stability of the driving scheme. The result shows that OLED current is stable after 120-hour operation. The VT shift of the driving transistor is 0.7 V.

FIG. **6** illustrates a display system having the pixel circuit **200** of FIG. **3**. VDD**1** and VDD**2** of FIG. **6** correspond to VDD of FIG. **3**. SEL**1** and SEL**2** of FIG. **6** correspond to SEL of FIG. **3**. VDATA**1** and VDATA**2** of FIG. **6** correspond to VDATA of FIG. **3**. The array of FIG. **6** is an active matrix light emitting diode (AMOLED) display having a plurality of the pixel circuits **200** of FIG. **3**. The pixel circuits are arranged in rows and columns, and interconnections **41**, **42** and **43** (VDATA**1**, SEL**1**, VDD**1**). VDATA**1** (or VDATA **2**) is shared between the common column pixels while SEL**1** (or SEL**2**) and VDD**1** (or VDD**2**) are shared between common row pixels in the array structure.

A driver **300** is provided for driving VDATA**1** and VDATA**2**. A driver **302** is provided for driving VDD**1**, VDD**2**, SEL**1** and SEL**2**, however, the driver for VDD and SEL lines can also be implemented separately. A controller **304** controls the drivers **300** and **302** to programming and driving the pixel circuits as described above. The timing diagram for programming and driving the display array of FIG. **6** is as shown in FIG. **2**. Each programming and driving cycle may be the same as that of FIG. **4**.

FIG. **7**(*a*) illustrates an example of array structure having top emission pixels are arranged. FIG. **7**(*b*) illustrates an example of array structure having bottom emission pixels are arranged. The array of FIG. **6** may have array structure shown in FIG. **7**(*a*) or **7**(*b*). In FIG. **7**(*a*), **400** represents a substrate, **402** represents a pixel contact, **403** represents a (top emission) pixel circuit, and **404** represents a transparent top electrode on the OLEDs. In FIG. **7**(*b*), **410** represents a transparent substrate, **411** represents a (bottom emission) pixel circuit, and **412** represents a top electrode. All of the pixel circuits including the TFTs, the storage capacitor, the SEL, VDATA, and VDD lines are fabricated together. After that, the OLEDs are fabricated for all pixel circuits. The OLED is connected to the corresponding driving transistor using a via (e.g. B**1** of FIG. **3**) as shown in FIGS. **7**(*a*) and **7**(*b*). The panel is finished by deposition of the top electrode on the OLEDs which can be a continuous layer, reducing the complexity of the design and can be used to turn the entire display ON/OFF or control the brightness.

FIG. **8** illustrates a pixel circuit **202** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **202** includes an OLED **50**, two storage capacitors **52** and **53**, a driving transistor **54**, and switch transistors **56** and **58**. The pixel circuit **202** is a top emission, voltage programmed pixel circuit. This embodiment principally works in the same manner as that of FIG. **3**. However, in the pixel circuit **202**, the OLED **50** is connected to the drain terminal of the driving transistor **54**. As a result, the circuit can be connected to the cathode Of the OLED **50**. Thus, the OLED deposition can be started with the cathode.

The transistors **54**, **56** and **58** are n-type TFTs. However, the transistors **54**; **56** and **58** may be p-type transistors The driving technique applied to the pixel circuit **202** is also applicable to a complementary pixel circuit having p-type transistors as shown in FIG. **17**. The transistors **54**, **56** and **58** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), NMOS/PMOS technology or CMOS technology (e.g. MOSFET).

The first terminal of the driving transistor **54** is connected to the cathode electrode of the OLED **50**. The second terminal of the driving transistor **54** is connected to a controllable voltage supply line VSS. The gate terminal of the driving transistor **54** is connected to its first line (terminal) through the switch transistor **56**. The storage capacitors **52** and **53** are in series, and are connected between the gate terminal of the driving transistor **54** and a common ground. The voltage on the voltage supply line VSS is controllable. The common ground may be connected to VSS.

The gate terminal of the switch transistor **56** is connected to a first select line SEL**1**. The first terminal of the switch transistor **56** is connected to the drain terminal of the driving transistor **54**. The second terminal of the switch transistor **56** is connected to the gate terminal of the driving transistor **54**.

The gate terminal of the switch transistor **58** is connected to a second select line SEL**2**. The first terminal of the switch transistor **58** is connected to a signal line VDATA. The second terminal of the switch transistor **58** is connected to the shared terminal of the storage capacitors **52** and **53** (i.e. node C**2**). The anode electrode of the OLED **50** is connected to a voltage supply electrode VDD.

The OLED **50** and the transistors **54** and **56** are connected at node A**2**. The storage capacitor **52** and the transistors **54** and **56** are connected at node B**2**.

FIG. **9** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **202** of FIG. **8**. Referring to FIGS. **8** and **9**, the operation of the pixel circuit **202** includes a programming cycle having four operating cycles X**21**, X**22**, X**23** and X**24**, and a driving cycle having one operating cycle X**25**.

During the programming cycle, a programming voltage plus the threshold voltage of the driving transistor **54** is stored in the storage capacitor **52**. The source terminal of the driving transistor **54** goes to zero, and the second storage capacitor **53** is charged to zero.

As a result, the gate-source voltage of the driving transistor **54** goes to:

$$VGS=VP+VT \tag{2}$$

where VGS represents the gate-source voltage of the driving transistor **54**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **54**.

In the first operating cycle X**21**: VSS goes to a high positive voltage, and VDATA is zero. SEL**1** and SEL**2** are high. Therefore, nodes A**2** and B**2** are charged to a positive voltage.

In the second operating cycle X**22**: While SEL**1** is low and the switch transistor **56** is off, VDATA goes to a high positive voltage. As a result, the voltage at node B**2** increases (i.e. bootstrapping) and node A**2** is charged to the voltage of VSS. At this voltage, the OLED **50** is off.

In the third operating cycle X**23**: VSS goes to a reference voltage VREF. VDATA goes to (VREF−VP). At the beginning of this cycle, the voltage of node B**2** becomes almost equal to the voltage of node A**2** because the capacitance **51** of the OLED **50** is bigger than that of the storage capacitor **52**. After that, the voltage of node B**2** and the voltage of node A**2** are discharged through the driving transistor **54** until the driving transistor **54** turns off. As a result, the gate-source voltage of the driving transistor **54** is (VREF+VT), and the voltage stored in storage capacitor **52** is (VP+VT).

In the fourth operating cycle X**24**: SEL**1** is low. Since SEL**2** is high, and VDATA is zero, the voltage at node C**2** goes to zero.

In the fifth operating cycle X**25**: VSS goes to its operating voltage during the driving cycle. In FIG. **5**, the operating voltage of VSS is zero. However, it may be any voltage other than zero. SEL**2** is low. The voltage stored in the storage capacitor **52** is applied to the gate terminal of the driving transistor **54**. Accordingly, a current independent of the threshold voltage VT of the driving transistor **54** and the voltage of the OLED **50** flows through the driving transistor **54** and the OLED **50**. Thus, the degradation of the OLED **50** and instability of the driving transistor **54** does not affect the amount of the current flowing through the driving transistor **54** and the OLED **50**.

FIG. **10** illustrates a pixel circuit **204** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **204** includes an OLED **60**, two storage capacitors **62** and **63**, a driving transistor **64**, and switch transistors **66** and **68**. The pixel circuit **204** is a top emission, voltage programmed pixel circuit. The pixel circuit **204** principally works similar to that of in FIG. **8**. However, one common select line is used to operate the pixel circuit **204**, which can increase the available pixel area and aperture ratio.

The transistors **64**, **66** and **68** are n-type TFTs. However, The transistors **64**, **66** and **68** may be p-type transistors. The driving technique applied to the pixel circuit **204** is also applicable to a complementary pixel circuit having p-type transistors as shown in FIG. **19**. The transistors **64**, **66** and **68** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), NMOS/PMOS technology or CMOS technology (e.g. MOSFET).

The first terminal of the driving transistor **64** is connected to the cathode electrode of the OLED **60**. The second terminal of the driving transistor **64** is connected to a controllable voltage supply line VSS. The gate terminal of the driving transistor **64** is connected to its first line (terminal) through the switch transistor **66**. The storage capacitors **62** and **63** are in series, and are connected between the gate terminal of the driving transistor **64** and the common ground. The voltage of the voltage supply line VSS is controllable. The common ground may be connected to VSS.

The gate terminal of the switch transistor **66** is connected to a select line SEL. The first terminal of the switch transistor **66** is connected to the first terminal of the driving transistor **64**. The second terminal of the switch transistor **66** is connected to the gate terminal of the driving transistor **64**.

The gate terminal of the switch transistor **68** is connected to the select line SEL. The first terminal of the switch transistor **68** is connected to a signal line VDATA. The second terminal is connected to the shared terminal of storage capacitors **62** and **63** (i.e. node C**3**). The anode electrode of the OLED **60** is connected to a voltage supply electrode VDD.

The OLED **60** and the transistors **64** and **66** are connected at node A**3**. The storage capacitor **62** and the transistors **64** and **66** are connected at node B**3**.

FIG. **11** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **204** of FIG. **10**. Referring to FIGS. **10** and **11**, the operation of the pixel circuit **204** includes a programming cycle having three operating cycles X**31**, X**32** and X**33**, and a driving cycle includes one operating cycle X**34**.

During the programming cycle, a programming voltage plus the threshold voltage of the driving transistor **64** is stored in the storage capacitor **62**. The source terminal of the driving transistor **64** goes to zero and the storage capacitor **63** is charged to zero.

As a result, the gate-source voltage of the driving transistor **64** goes to:

$$VGS=VP+VT \tag{3}$$

where VGS represents the gate-source voltage of the driving transistor **64**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **64**.

In the first operating cycle X**31**: VSS goes to a high positive voltage, and VDATA is zero. SEL is high. As a result, nodes A**3** and B**3** are charged to a positive voltage. The OLED **60** turns off.

In the second operating cycle X**32**: While SEL is high, VSS goes to a reference voltage VREF. VDATA goes to (VREF−VP). As a result, the voltage at node B**3** and the voltage of node A**3** are discharged through the driving transistor **64** until the driving transistor **64** turns off. The voltage of node B**3** is (VREF+VT), and the voltage stored in the storage capacitor **62** is (VP+VT).

In the third operating cycle X**33**: SEL goes to VM. VM is an intermediate voltage in which the switch transistor **66** is off and the switch transistor **68** is on. VDATA goes to zero. Since SEL is VM and VDATA is zero, the voltage of node C3 goes to zero.

VM is defined as:

$$VT3 \ll VM < VREF + VT1 + VT2 \qquad (a)$$

where VT**1** represents the threshold voltage of the driving transistor **64**, VT**2** represents the threshold voltage of the switch transistor **66**, and VT**3** represents the threshold voltage of the switch transistor **68**.

The condition (a) forces the switch transistor **66** to be off and the switch transistor **68** to be on. The voltage stored in the storage capacitor **62** remains intact.

In the fourth operating cycle X**34**: VSS goes to its operating voltage during the driving cycle. In FIG. **11**, the operating voltage of VSS is zero. However, the operating voltage of VSS may be any voltage other than zero. SEL is low. The voltage stored in the storage capacitor **62** is applied to the gate of the driving transistor **64**. The driving transistor **64** is ON. Accordingly, a current independent of the threshold voltage VT of the driving transistor **64** and the voltage of the OLED **60** flows through the driving transistor **64** and the OLED **60**. Thus, the degradation of the OLED **60** and instability of the driving transistor **64** does not affect the amount of the current flowing through the driving transistor **64** and the OLED **60**.

FIG. **12** illustrates a pixel circuit **206** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **206** includes an OLED **70**, two storage capacitors **72** and **73**, a driving transistor **74**, and switch transistors **76** and **78**. The pixel circuit **206** is a top emission, voltage programmed pixel circuit.

The transistors **74**, **76** and **78** are n-type TFTs. However, the transistors **74**, **76** and **78** may be p-type transistors. The driving technique applied to the pixel circuit **206** is also applicable to a complementary pixel circuit having p-type transistors as shown in FIG. **21**. The transistors **74**, **76** and **78** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), NMOS/PMOS technology or CMOS technology (e.g. MOSFET).

The first terminal of the driving transistor **74** is connected to the cathode electrode of the OLED **70**. The second terminal of the driving transistor **74** is connected to a common ground. The gate terminal of the driving transistor **74** is connected to its first line (terminal) through the switch transistor **76**. The storage capacitors **72** and **73** are in series, and are connected between the gate terminal of the driving transistor **74** and the common ground.

The gate terminal of the switch transistor **76** is connected to a select line SEL. The first terminal of the switch transistor **76** is connected to the first terminal of the driving transistor **74**. The second terminal of the switch transistor **76** is connected to the gate terminal of the driving transistor **74**.

The gate terminal of the switch transistor **78** is connected to the select line SEL. The first terminal of the switch transistor **78** is connected to a signal line VDATA. The second terminal is connected to the shared terminal of storage capacitors **72** and **73** (i.e. node C**4**). The anode electrode of the OLED **70** is connected to a voltage supply electrode VDD. The voltage of the voltage electrode VDD is controllable.

The OLED **70** and the transistors **74** and **76** are connected at node A**4**. The storage capacitor **72** and the transistors **74** and **76** are connected at node B**4**.

FIG. **13** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **206** of FIG. **12**. Referring to FIGS. **12** and **13**, the operation of the pixel circuit **206** includes a programming cycle having four operating cycles X**41**, X**42**, X**43** and X**44**, and a driving cycle having one driving cycle **45**.

During the programming cycle, a programming voltage plus the threshold voltage of the driving transistor **74** is stored in the storage capacitor **72**. The source terminal of the driving transistor **74** goes to zero and the storage capacitor **73** is charged to zero.

As a result, the gate-source voltage of the driving transistor **74** goes to:

$$VGS = VP + VT \qquad (4)$$

where VGS represents the gate-source voltage of the driving transistor **74**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **74**.

In the first operating cycle X**41**: SEL is high. VDATA goes to a low voltage. While VDD is high, node B**4** and node A**4** are charged to a positive voltage.

In the second operating cycle X**42**: SEL is low, and VDD goes to a reference voltage VREF where the OLED **70** is off.

In the third operating cycle X**43**: VDATA goes to (VREF**2**−VP) where VREF**2** is a reference voltage. It is assumed that VREF**2** is zero. However, VREF**2** can be any voltage other than zero. SEL is high. Therefore, the voltage of node B**4** and the voltage of node A**4** become equal at the beginning of this cycle. It is noted that the first storage capacitor **72** is large enough so that its voltage becomes dominant. After that, node B**4** is discharged through the driving transistor **74** until the driving transistor **74** turns off.

As a result, the voltage of node B**4** is VT (i.e. the threshold voltage of the driving transistor **74**). The voltage stored in the first storage capacitor **72** is (VP−VREF**2**+VT)=(VP+VT) where VREF**2**=0.

In the fourth operating cycle X**44**: SEL goes to VM where VM is an intermediate voltage at which the switch transistor **76** is off and the switch transistor **78** is on. VM satisfies the following condition:

$$VT3 \ll VM < VP + VT \qquad (b)$$

where VT**3** represents the threshold voltage of the switch transistor **78**.

VDATA goes to VREF**2** (=0). The voltage of node C**4** goes to VREF**2** (=0).

This results in that the gate-source voltage VGS of the driving transistor **74** is (VP+VT). Since VM<VP+VT, the switch transistor **76** is off, and the voltage stored in the storage capacitor **72** stays at VP+VT.

In the fifth operating cycle X**45**: VDD goes to the operating voltage. SEL is low. The voltage stored in the storage capacitor **72** is applied to the gate of the driving transistor **74**. Accordingly, a current independent of the threshold voltage VT of the driving transistor **74** and the voltage of the OLED **70** flows through the driving transistor **74** and the OLED **70**. Thus, the degradation of the OLED **70** and instability of the driving transistor **74** does not affect the amount of the current flowing through the driving transistor **74** and the OLED **70**.

FIG. **14** illustrates a pixel circuit **208** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **208** includes an OLED **80**, a storage capacitor **81**, a driving transistor **84** and a switch transistor **86**. The pixel circuit **208** corresponds to the pixel circuit **200** of FIG. **3**, and a voltage programmed pixel circuit.

The transistors **84** and **86** are p-type TFTs. The transistors **84** and **86** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), CMOS technology (e.g. MOSFET) and any other technology which provides p-type transistors.

The first terminal of the driving transistor **84** is connected to a controllable voltage supply line VSS. The second terminal of the driving transistor **84** is connected to the cathode electrode of the OLED **80**. The gate terminal of the driving transistor **84** is connected to a signal line VDATA through the switch transistor **86**. The storage capacitor **81** is connected between the second terminal and the gate terminal of the driving transistor **84**.

The gate terminal of the switch transistor **86** is connected to a select line SEL. The first terminal of the switch transistor **86** is connected to the signal line VDATA. The second terminal of the switch transistor **86** is connected to the gate terminal of the driving transistor **84**. The anode electrode of the OLED **80** is connected to a ground voltage supply electrode.

The storage capacitor **81** and the transistors **84** and **85** are connected at node A**5**. The OLED **80**, the storage capacitor **81** and the driving transistor **84** are connected at node B**5**.

FIG. **15** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **208** of Figure. FIG. **15** corresponds to FIG. **4**. VDATA and VSS are used to programming and compensating for a time dependent parameter of the pixel circuit **208**, which are similar to VDATA and VDD of FIG. **4**. Referring to FIGS. **14** and **15**, the operation of the pixel circuit **208** includes a programming cycle having three operating cycles X**51**, X**52** and X**53**, and a driving cycle having one operating cycle X**54**.

During the programming cycle, node B**5** is charged to a positive threshold voltage of the driving transistor **84**, and node A**5** is charged to a negative programming voltage.

As a result, the gate-source voltage of the driving transistor **84** goes to:

$$VGS=-VP+(-|VT|)=-VP-|VT| \tag{5}$$

where VGS represents the gate-source voltage of the driving transistor **84**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **84**.

In the first operating cycle X**51**: VSS goes to a positive compensating voltage VCOMPB, and VDATA goes to a negative compensating voltage (−VCOMPA), and SEL is low. As a result, the switch transistor **86** is on. Node A**5** is charged to (−VCOMPA). Node B**5** is charged to VCOMPB.

In the second operating cycle X**52**: VDATA goes to a reference voltage VREF. Node B**5** is discharged through the driving transistor **84** until the driving transistor **84** turns off. As a result, the voltage of node B**5** reaches VREF+|VT|. VSS goes to a negative voltage VL to increase the speed of this cycle X**52**. For the optimal setting time, VL is selected to be equal to the operating voltage which is the voltage of VSS during the driving cycle.

In the third operating cycle X**53**: While VSS is in the VL level, and SEL is low, node A**5** is charged to (VREF−VP). Because the capacitance **82** of the OLED **80** is large, the voltage of node B**5** stays at the positive threshold voltage of the driving transistor **84**. Therefore, the gate-source voltage of the driving transistor **84** is (−VP−VT|), which is stored in storage capacitor **81**.

In the fourth operating cycle X**54**: SEL and VDATA go to zero. VSS goes to a high negative voltage (i.e. its operating voltage). The voltage stored in the storage capacitor **81** is applied to the gate terminal of the driving transistor **84**. Accordingly, a current independent of the voltage of the OLED **80** and the threshold voltage of the driving transistor **84** flows through the driving transistor **84** and the OLED **80**. Thus, the degradation of the OLED **80** and instability of the driving transistor **84** does not affect the amount of the current flowing through the driving transistor **84** and the OLED **80**.

It is noted that the pixel circuit **208** can be operated with different values of VCOMPB, VCOMPA, VL, VREF and VP. VCOMPB, VCOMPA, VL, VREF and VP define the lifetime of the pixel circuit. Thus, these voltages can be defined in accordance with the pixel specifications.

FIG. **16** illustrates a display system having the pixel circuit **208** of FIG. **14**. VSS1 and VSS2 of FIG. **16** correspond to VSS of FIG. **14**. SEL**1** and SEL**2** of FIG. **16** correspond to SEL of FIG. **14**. VDATA**1** and VDATA**2** of FIG. **16** correspond to VDATA of FIG. **14**. The array of FIG. **16** is an active matrix light emitting diode (AMOLED) display having a plurality of the pixel circuits **208** of FIG. **14**. The pixel circuits **208** are arranged in rows and columns, and interconnections **91**, **92** and **93** (VDATA**1**, SEL**2**, VSS**2**). VDATA**1** (or VDATA**2**) is shared between the common column pixels while SEL**1** (or SEL**2**) and VSS**1** (or VSS**2**) are shared between common row pixels in the array structure.

A driver **310** is provided for driving VDATA**1** and VDATA**2**. A driver **312** is provided for driving VSS**1**, VSS**2**, SEL**1** and SEL**2**. A controller **314** controls the drivers **310** and **312** to implement the programming and driving cycles described above. The timing diagram for programming and driving the display array of FIG. **6** is as shown in FIG. **2**. Each programming and driving cycle may be the same as that of FIG. **15**.

The array of FIG. **16** may have array structure shown in FIG. **7**(*a*) or **7**(*b*). The array of FIG. **16**, is produced in a manner similar to that of FIG. **6**. All of the pixel circuits including the TFTs, the storage capacitor, the SEL, VDATA, and VSS lines are fabricated together. After that, the OLEDs are fabricated for all pixel circuits. The OLED is connected to the corresponding driving transistor using a via (e.g. B**5** of FIG. **14**). The panel is finished by deposition of the top electrode on the OLEDs which can be a continuous layer, reducing the complexity of the design and can be used to turn the entire display ON/OFF or control the brightness.

FIG. **17** illustrates a pixel circuit **210** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **210** includes an OLED **100**, two storage capacitors **102** and **103**, a driving transistor **104**, and switch transistors **106** and **108**. The pixel circuit **210** corresponds to the pixel circuit **202** of FIG. **8**.

The transistors **104**, **106** and **108** are p-type TFTs. The transistors **84** and **86** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), CMOS technology (e.g. MOSFET) and any other technology which provides p-type transistors.

In FIG. **17**, one of the terminals of the driving transistor **104** is connected to the anode electrode of the OLED **100**, while the other terminal is connected to a controllable voltage supply line VDD. The storage capacitors **102** and **103** are in series, and are connected between the gate terminal of the driving transistor **104** and a voltage supply electrode V**2**. Also, V**2** may be connected to VDD. The cathode electrode of the OLED **100** is connected to a ground voltage supply electrode.

The OLED **100** and the transistors **104** and **106** are connected at node A**6**. The storage capacitor **102** and the transistors **104** and **106** are connected at node B**6**. The transistor **108** and the storage capacitors **102** and **103** are connected at node C**6**.

FIG. **18** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **210** of FIG. **17**. FIG. **18** corresponds to FIG. **9**. VDATA and VDD are used to programming and compensating for a time dependent parameter of the pixel circuit **210**, which are similar to VDATA and VSS of FIG. **9**. Referring to FIGS. **17** and **18**, the operation of the pixel circuit **210** includes a programming cycle having four operating cycles X**61**, X**62**, X**63** and X**64**, and a driving cycle having one operating cycle X**65**.

During the programming cycle, a negative programming voltage plus the negative threshold voltage of the driving transistor **104** is stored in the storage capacitor **102**, and the second storage capacitor **103** is discharged to zero.

As a result, the gate-source voltage of the driving transistor **104** goes to:

$$VGS=-VP-|VT| \tag{6}$$

where VGS represents the gate-source voltage of the driving transistor **104**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **104**.

In the first operating cycle X**61**: VDD goes to a high negative voltage, and VDATA is set to V**2**. SEL**1** and SEL**2** are low. Therefore, nodes A**6** and B**6** are charged to a negative voltage.

In the second operating cycle X**62**: While SEL**1** is high and the switch transistor **106** is off, VDATA goes to a negative voltage. As a result, the voltage at node B**6** decreases, and the voltage of node A**6** is charged to the voltage of VDD. At this voltage, the OLED **100** is off.

In the third operating cycle X**63**: VDD goes to a reference voltage VREF. VDATA goes to (V2−VREF+VP) where VREF is a reference voltage. It is assumed that VREF is zero. However, VREF may be any voltage other than zero. At the beginning of this cycle, the voltage of node B**6** becomes almost equal to the voltage of node A**6** because the capacitance **101** of the OLED **100** is bigger than that of the storage capacitor **102**. After that, the voltage of node B**6** and the voltage of node A**6** are charged through the driving transistor **104** until the driving transistor **104** turns off. As a result, the gate-source voltage of the driving transistor **104** is (−VP−|VT|), which is stored in the storage capacitor **102**.

In the fourth operating cycle X**64**: SEL**1** is high. Since SEL**2** is low, and VDATA goes to V**2**, the voltage at node C**6** goes to V**2**.

In the fifth operating cycle X**65**: VDD goes to its operating voltage during the driving cycle. In FIG. **18**, the operating voltage of VDD is zero. However, the operating voltage of VDD may be any voltage. SEL**2** is high. The voltage stored in the storage capacitor **102** is applied to the gate terminal of the driving transistor **104**. Thus, a current independent of the threshold voltage VT of the driving transistor **104** and the voltage of the OLED **100** flows through the driving transistor **104** and the OLED **100**. Accordingly, the degradation of the OLED **100** and instability of the driving transistor **104** do not affect the amount of the current flowing through the driving transistor **54** and the OLED **100**.

FIG. **19** illustrates a pixel circuit **212** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **212** includes an OLED **110**, two storage capacitors **112** and **113**, a driving transistor **114**, and switch transistors **116** and **118**. The pixel circuit **212** corresponds to the pixel circuit **204** of FIG. **10**.

The transistors **114**, **116** and **118** are p-type TFTs. The transistors **84** and **86** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), CMOS technology (e.g. MOSFET) and any other technology which provides p-type transistors.

In FIG. **19**, one of the terminals of the driving transistor **114** is connected to the anode electrode of the OLED **110**, while the other terminal is connected to a controllable voltage supply line VDD. The storage capacitors **112** and **113** are in series, and are connected between the gate terminal of the driving transistor **114** and a voltage supply electrode V**2**. Also, V**2** may be connected to VDD. The cathode electrode of the OLED **100** is connected to a ground voltage supply electrode.

The OLED **110** and the transistors **114** and **116** are connected at node A**7**. The storage capacitor **112** and the transistors **114** and **116** are connected at node B**7**. The transistor **118** and the storage capacitors **112** and **113** are connected at node C**7**.

FIG. **20** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **212** of FIG. **19**. FIG. **20** corresponds to FIG. **11**. VDATA and VDD are used to programming and compensating for a time dependent parameter of the pixel circuit **212**, which are similar to VDATA and VSS of FIG. **11**. Referring to FIGS. **19** and **20**, the operation of the pixel circuit **212** includes a programming cycle having four operating cycles X**71**, X**72** and X**73**, and a driving cycle having one operating cycle X**74**.

During the programming cycle, a negative programming voltage plus the negative threshold voltage of the driving transistor **114** is stored in the storage capacitor **112**. The storage capacitor **113** is discharged to zero.

As a result, the gate-source voltage of the driving transistor **114** goes to:

$$VGS=-VP-|VT| \tag{7}$$

where VGS represents the gate-source voltage of the driving transistor **114**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **114**.

In the first operating cycle X**71**: VDD goes to a negative voltage. SEL is low. Node A**7** and node B**7** are charged to a negative voltage.

In the second operating cycle X**72**: VDD goes to a reference voltage VREF. VDATA goes to (V2−VREF+VP). The voltage at node B**7** and the voltage of node A**7** are changed until the driving transistor **114** turns off. The voltage of B**7** is (−VREF−VT), and the voltage stored in the storage capacitor **112** is (−VP−|VT|).

In the third operating cycle X**73**: SEL goes to VM. VM is an intermediate voltage in which the switch transistor **106** is off and the switch transistor **118** is on. VDATA goes to V**2**. The voltage of node C**7** goes to V**2**. The voltage stored in the storage capacitor **112** is the same as that of X**72**.

In the fourth operating cycle X**74**: VDD goes to its operating voltage. SEL is high. The voltage stored in the storage capacitor **112** is applied to the gate of the driving transistor **114**. The driving transistor **114** is on. Accordingly, a current independent of the threshold voltage VT of the driving transistor **114** and the voltage of the OLED **110** flows through the driving transistor **114** and the OLED **110**.

FIG. **21** illustrates a pixel circuit **214** to which programming and driving technique in accordance with a further embodiment of the present invention is applied. The pixel circuit **214** includes an OLED **120**, two storage capacitors **122** and **123**, a driving transistor **124**, and switch transistors **126** and **128**. The pixel circuit **212** corresponds to the pixel circuit **206** of FIG. **12**.

The transistors **124**, **126** and **128** are p-type TFTs. The transistors **84** and **86** may be fabricated using amorphous silicon, nano/micro crystalline silicon, poly silicon, organic semiconductors technologies (e.g. organic TFT), CMOS technology (e.g. MOSFET) and any other technology which provides p-type transistors.

In FIG. **21**, one of the terminals of the driving transistor **124** is connected to the anode electrode of the OLED **120**, while the other terminal is connected to a voltage supply line VDD. The storage capacitors **122** and **123** are in series, and are connected between the gate terminal of the driving transistor **124** and VDD. The cathode electrode of the OLED **120** is connected to a controllable voltage supply electrode VSS.

The OLED **120** and the transistors **124** and **126** are connected at node A**8**. The storage capacitor **122** and the transistors **124** and **126** are connected at node B**8**. The transistor **128** and the storage capacitors **122** and **123** are connected at node C**8**.

FIG. **22** illustrates a timing diagram showing an example of waveforms for programming and driving the pixel circuit **214** of FIG. **21**. FIG. **22** corresponds to FIG. **13**. VDATA and VSS are used to programming and compensating for a time dependent parameter of the pixel circuit **214**, which are similar to VDATA and VDD of FIG. **13**. Referring to FIGS. **21** and **22**, the programming of the pixel circuit **214** includes a programming cycle having four operating cycles X**81**, X**82**, X**83** and X**84**, and a driving cycle having one driving cycle X**85**.

During the programming cycle, a negative programming voltage plus the negative threshold voltage of the driving transistor **124** is stored in the storage capacitor **122**. The storage capacitor **123** is discharged to zero.

As a result, the gate-source voltage of the driving transistor **124** goes to:

$$VGS=-VP-|VT| \tag{8}$$

where VGS represents the gate-source voltage of the driving transistor **114**, VP represents the programming voltage, and VT represents the threshold voltage of the driving transistor **124**.

In the first operating cycle X**81**: VDATA goes to a high voltage. SEL is low. Node A**8** and node B**8** are charged to a positive voltage.

In the second operating cycle X**82**: SEL is high. VSS goes to a reference voltage VREF**1** where the OLED **60** is off.

In the third operating cycle X**83**: VDATA goes to (VREF2+VP) where VREF**2** is a reference voltage. SEL is low. Therefore, the voltage of node B**8** and the voltage of node A**8** become equal at the beginning of this cycle. It is noted that the first storage capacitor **112** is large enough so that its voltage becomes dominant. After that, node B**8** is charged through the driving transistor **124** until the driving transistor **124** turns off. As a result, the voltage of node B**8** is (VDD−|VT|). The voltage stored in the first storage capacitor **122** is (−VREF2−VP−|VT|).

In the fourth operating cycle X**84**: SEL goes to VM where VM is an intermediate voltage at which the switch transistor **126** is off and the switch transistor **128** is on. VDATA goes to VREF**2**. The voltage of node C**8** goes to VREF**2**.

This results in that the gate-source voltage VGS of the driving transistor **124** is (−VP−|VT|). Since VM<−VP−VT, the switch transistor **126** is off, and the voltage stored in the storage capacitor **122** stays at −(VP+|VT|).

In the fifth operating cycle X**85**: VSS goes to the operating voltage. SEL is low. The voltage stored in the storage capacitor **122** is applied to the gate of the driving transistor **124**.

It is noted that a system for operating an array having the pixel circuit of FIG. **8**, **10**, **12**, **17**, **19** or **21** may be similar to that of FIG. **6** or **16**. The array having the pixel circuit of FIG. **8**, **10**, **12**, **17**, **19** or **21** may have array structure shown in FIG. **7**(*a*) or **7**(*b*).

It is noted that each transistor can be replaced with p-type or n-type transistor based on concept of complementary circuits.

According to the embodiments of the present invention, the driving transistor is in saturation regime of operation. Thus, its current is defined mainly by its gate-source voltage VGS. As a result, the current of the driving transistor remains constant even if the OLED voltage changes since its gate-source voltage is stored in the storage capacitor.

According to the embodiments of the present invention, the overdrive voltage providing to a driving transistor is generated by applying a waveform independent of the threshold voltage of the driving transistor and/or the voltage of a light emitting diode voltage.

According to the embodiments of the present invention, a stable driving technique based on bootstrapping is provided (e.g. FIGS. **2-12** and **16-20**).

The shift(s) of the characteristic(s) of a pixel element(s) (e.g. the threshold voltage shift of a driving transistor and the degradation of a light emitting device under prolonged display operation) is compensated for by voltage stored in a storage capacitor and applying it to the gate of the driving transistor. Thus, the pixel circuit can provide a stable current though the light emitting device without any effect of the shifts, which improves the display operating lifetime. Moreover, because of the circuit simplicity, it ensures higher product yield, lower fabrication cost and higher resolution than conventional pixel circuits.

All citations are hereby incorporated by reference.

The present invention has been described with regard to one or more embodiments. However, it will be apparent to persons skilled in the art that a number of variations and modifications can be made without departing from the scope of the invention as defined in the claims.

What is claimed is:

1. A method of programming a pixel circuit that drives a current-driven organic light emitting device independent of a threshold voltage of a drive transistor connected in series to the organic light emitting device, the pixel circuit further including a first switch transistor connected between the organic light emitting device and a node of the pixel circuit, the method comprising:

adjusting during a programming cycle a controllable voltage supply to a compensation voltage;

in a first operating cycle of the programming cycle, selecting a select line, to turn on a second switch transistor coupled to the drive transistor, for applying a reference voltage to the drive transistor through the second switch transistor, and to turn on the first switch transistor, and applying to a data line connected to the second switch transistor a voltage that exceeds a programming voltage to be applied to the drive transistor;

responsive to the adjusting, allowing the node of the pixel circuit to charge or discharge through the drive transistor, via the first switch transistor, until the drive transistor turns off, thereby establishing the threshold voltage of the drive transistor across the drive transistor;

in a further operating cycle of the programming cycle following the first operating cycle, selecting the select line to turn on the second switch transistor for applying a programming voltage from the data line to the drive transistor through the second switch transistor, thereby establishing a fixed voltage applied to the drive transistor according to both the threshold voltage and the applied programming voltage, wherein the programming voltage is lower than the reference voltage;

responsive to the applying the programming voltage, selecting the select line with an intermediate selection voltage being sufficient to turn on the second switch transistor while turning off the first switch transistor; and

applying a second reference voltage, via the data line, to allow the fixed voltage in the pixel circuit to be independent of the reference voltage.

2. The method of claim **1**, further comprising:

setting the controllable voltage supply to an operating voltage; and

deselecting the select line to complete the programming cycle and initiate a drive cycle during which the light emitting device is turned on according to the programming voltage while maintaining the fixed voltage on the drive transistor.

3. The method of claim **2**, wherein the compensation voltage is sufficient to prevent the organic light emitting device from being turned on prior to the initiation of the drive cycle.

4. The method of claim **1**, wherein the pixel circuit includes a storage capacitor coupled to the gate terminal of the drive transistor, and wherein the node of the pixel circuit is coupled to the gate terminal of the transistor such that the allowing the node of the pixel circuit to discharge is carried out by charging the storage capacitor through the first switch transistor and the drive transistor.

5. The method of claim **1**, wherein a voltage stored on the node following the drive transistor turning off is different from the voltage on a voltage supply line connected to a terminal of the drive transistor opposite the organic light emitting device by the threshold voltage of the drive transistor.

6. The method of claim **1**, wherein the select line remains selected during the allowing the node to charge or discharge and the applying the programming voltage.

7. The method of claim **1**, wherein the pixel circuit includes a storage capacitor coupled between the second switch transistor and the node of the pixel circuit for being charged with the fixed voltage, and a first capacitor coupled between a voltage supply line connected to the drive transistor opposite the light emitting device and the storage capacitor, the second switch transistor connected to a node between the first capacitor and the storage capacitor, and wherein the applying the second reference voltage discharges the first capacitor and leaves the fixed voltage on the storage capacitor.

8. A display system comprising:

a pixel circuit including a drive transistor, a light emitting device, a first switch transistor, and a second switch transistor,

the drive transistor having a first terminal connected to the light-emitting device, the drive transistor having a threshold voltage that shifts during operation of the drive transistor,

the first switch transistor coupled between a data line and the second switch transistor, and

the second switch transistor having a first terminal connected to the first terminal of the drive transistor and a second terminal connected to a gate terminal of the drive transistor, such that, during a compensation cycle of a programming cycle while the second switch transistor is selected via a select line and while a high voltage, which exceeds a programming voltage to be applied to the drive transistor through the first switch transistor, is applied to the data line, the second switch transistor is allowed to charge or discharge a node of the pixel circuit, through the drive transistor, via the second switch transistor, until the drive transistor turns off, thereby establishing the threshold voltage of the drive transistor between the gate terminal and the first terminal of the drive transistor;

during an operating cycle of the programming cycle following the compensation cycle, via an intermediate voltage on the select line, turning off the second switch transistor and turning on the first switch transistor for applying the programming voltage from the data line to the drive transistor through the first switch transistor, thereby establishing a fixed voltage applied to the drive transistor according to both the threshold voltage and the applied programming voltage, wherein the programming voltage is lower than the high voltage; and

a controllable power supply connected to the light-emitting device for supplying the drive transistor with a voltage that is adjusted to a compensation voltage sufficient to turn off the light emitting device, during the compensation cycle.

9. The display system of claim **8**, wherein the node that is charged or discharged, via the second switch transistor, is directly connected to the gate terminal of the drive transistor.

10. The display system of claim **8** in which the controllable voltage source maintains a substantially constant pixel current as the threshold voltage of the drive transistor changes with the aging of the drive transistor.

11. The display system of claim **8** in which the light-emitting device includes an OLED supplied with the stable pixel current from the drive transistor, and the stable pixel current maintains a substantially constant brightness of the light emitted by the OLED.

12. The display system of claim **8** in which the light-emitting device includes an OLED having a voltage V_{OLED} that increases as the OLED ages.

13. The display system of claim **8**, wherein the pixel circuit is configured to receive, via the first switch transistor, a reference voltage applied to a terminal of a storage capacitor, the storage capacitor being coupled to the gate terminal of the drive transistor such that the storage capacitor is charged according to the threshold voltage of the drive transistor during the compensation cycle.

14. The display system of claim **8**, wherein the pixel circuit further includes:

a storage capacitor coupled to the gate terminal of the drive transistor, the storage capacitor adapted to apply a voltage to the drive transistor during a driving cycle of the pixel circuit during which the pixel circuit is operated to drive the light emitting device to emit light according to programming information, wherein

the first switch transistor is adapted to selectively couple the data line to the storage capacitor during the compensation cycle and during the programming cycle of the pixel circuit during which the pixel circuit receives the programming voltage according to the programming information.

15. The display system of claim **8** wherein the light-emitting device is an organic light emitting diode and the drive transistor is an n-type or p-type thin film transistor.

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专利名称(译)	用于编程和驱动具有可控电源电压的有源矩阵发光装置像素的方法和系统		
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摘要(译)

提供了编程和驱动有源矩阵发光器件像素的方法和系统。像素是电压编程像素电路，并且具有发光器件，驱动晶体管和存储电容器。像素具有具有多个操作周期的编程周期和驱动周期。在编程周期期间，控制OLED和驱动晶体管之间的连接电压，使得驱动晶体管的期望的栅极 - 源极电压被存储在存储电容器中。